TM Vacuum Sputter Deposition LOG

Name/Date: Bennion Redd			Date:	6-30-11	Start Time	9:00 AM	End Time	Load lock BP	1×10^{-6}
Process Gas (es)	Ar	Substrate: SiO_2/PR		Deposition Pressure (mT) 10			End Time	Chamber BP	5.7×10^{-7}
Target Material #1	Ti	Time: 10 min				Presput Power Film #1:		Time:	
Deposition Power #1:	45W	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Au	Time: 5 min				Presput Power Film #2:		Time:	
Deposition Power #2:	50 W	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates: 1				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date: YAN XIE			Date:	7/1/2011	Start Time	1:30 PM	End Time 3:00 PM	Load lock BP	2.2×10^{-6}
Process Gas (es)	Ar	Substrate:	Si	Deposition Pressure (mT)		10		Chamber BP	5.7×10^{-7}
Target Material #1	Ti	Time:	15 min			Presput Power Film #1:		Time:	2 min
Deposition Power #1:	90W	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:				Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:			/	Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date: Precious Cantu			Date:	7/5/11	Start Time		End Time	Load lock BP	1.0×10^{-6}
Process Gas (es)	Ar	Substrate:	Si	Deposition Pressure (mT)		10mT		Chamber BP	[illegible]
Target Material #1	Pt	Time:	5 min 33sec			Presput Power Film #1:		Time:	5m 33sec
Deposition Power #1:	90w	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:				Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:			One	Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date: Sarelop (BP)			Date:	7/10/11	Start Time	10:30 am	End Time 3pm	Load lock BP	2×10^{-6}
Process Gas (es)	Ar/O_2	Substrate:	Si	Deposition Pressure (mT)				Chamber BP	2×10^{-7}
Target Material #1	Ti	Time:	10 min			Presput Power Film #1: 90W		Time:	2min
Deposition Power #1:	90W	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Ir	Time:	20 min			Presput Power Film #2: 100W		Time:	2min
Deposition Power #2:	100W	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:			ONE	Comments					
Total Sputter Time (all sample holders combined) Target #1			10 min	Total Sputter Time (all sample holders) Target #2				20 min	

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date:	[illegible] (BR)		Date:	6/27/11	Start Time	10:30 am	End Time	3:30 pm	Load lock BP 2x10
Process Gas (es)	Ar/O2	Substrate:	Si	Deposition Pressure (mT)			End Time		Chamber BP 2x10
Target Material #1	Ti	Time:			Presput Power Film #1: Ti				Time: 1 min
Deposition Power #1:	90 W	Time:	10 min	Film Thickness (nm):			Deposition rate (Å/s)		
Target Material #2	Ir	Time:			Presput Power Film #2:				Time: 2 min
Deposition Power #2:	100 W	Time:	20 min	Film Thickness (nm):			Deposition rate (Å/s)		
Number of Sample Holders With Substrates:	ONE			Comments	Ti (V: 572V, .16A)				
Total Sputter Time (all sample holders combined) Target #1	10 min			Total Sputter Time (all sample holders) Target #2					20 min

Prob
1) N_2 & O_2 flowing in chamber
Check for all valves etc

Name/Date:	Bennion Redd		Date:	6/29/11	Start Time	8:00 AM	End Time	9:45 AM	Load lock BP
Process Gas (es)	Ar/O_2	Substrate:	SiO_2/PR	Deposition Pressure (mT)					Chamber BP
Target Material #1	Ti	Time:			Presput Power Film #1:				Time:
Deposition Power #1:	45 W	Time:	7 min	Film Thickness (nm):			Deposition rate (Å/s)		
Target Material #2	Pt	Time:	19 min		Presput Power Film #2:				Time:
Deposition Power #2:	50 W	Time:		Film Thickness (nm):			Deposition rate (Å/s)		
Number of Sample Holders With Substrates:				Comments	Total thickness 200 nm				
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date:	Rohit Sharma		Date:	6/28/11	Start Time	2:30 pm	End Time	5:00 pm	Load lock BP 3x10 [-6]
Process Gas (es)	Ar	Substrate:	Si	Deposition Pressure (mT)			—	—	Chamber BP 4x10 [-7]
Target Material #1	Ti	Time:	10 min		Presput Power Film #1:				Time: 90W/10 mins
Deposition Power #1:	90W	~~Time:~~ Pr.	10 mT	Film Thickness (nm):			Deposition rate (Å/s)		
Target Material #2	Pt/Ag	Time:	90/90W		Presput Power Film #2:				Time: 2/2 min
Deposition Power #2:	10/6 mins	~~Time:~~ Pr.	11/20 mT	Film Thickness (nm):			Deposition rate (Å/s)		
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date:	Rohit Sharma		Date:	6/29/11	Start Time	11:00	End Time	1:00 pm	Load lock BP 3x10 [-6]
Process Gas (es)	Ar	Substrate:	Si	Deposition Pressure (mT)			—	—	Chamber BP 4x10 [-7]
Target Material #1	Ti	Time:	10 min		Presput Power Film #1:				Time: 90W/10 min
Deposition Power #1:	90W	~~Time:~~ Pr	10 mT	Film Thickness (nm):			Deposition rate (Å/s)		
Target Material #2	Pt/Ag	Time:	90/6 min		Presput Power Film #2:				Time: 90/90W – 2/2 min
Deposition Power #2:	90/90 W	~~Time:~~ Pr	11/6 mT	Film Thickness (nm):			Deposition rate (Å/s)		
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date:	Tan Xie		Date:	May 27, 11	Start Time	3PM	End Time	Load lock BP	1.2x10-6
Process Gas (es)	Ar	Substrate:	Glass	Deposition Pressure (mT)	10mT		End Time	Chamber BP	5.8x10 -7
Target Material #1	TiW	Time:		16S		Presput Power Film #1:		Time:	2 min
Deposition Power #1:	50W	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Au	Time:		2 min		Presput Power Film #2:		Time:	2 min
Deposition Power #2:	50W	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	2			Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date:	Je-Min Yoo		Date:	June 3, 11	Start Time	9:30	End Time 12:30	Load lock BP	1.2x10-6
Process Gas (es)	Ar/O2	Substrate:	Si	Deposition Pressure (mT)	10			Chamber BP	7.5x10-7
Target Material #1	Ti	Time:		10min		Presput Power Film #1:	60	Time:	10min
Deposition Power #1:	60	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Ir	Time:		22min		Presput Power Film #2:	100	Time:	12min
Deposition Power #2:	100	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	2			Comments	Left window shutter is not working				
Total Sputter Time (all sample holders combined) Target #1	20min			Total Sputter Time (all sample holders) Target #2	22min				

Name/Date:	Je-Min Yoo		Date:	June 6, 11	Start Time	9:00	End Time 12:10	Load lock BP	1.2x10-6
Process Gas (es)	Ar/O2	Substrate:	Si	Deposition Pressure (mT)				Chamber BP	8.0-9
Target Material #1	Ti	Time:		10min		Presput Power Film #1:	90	Time:	10min
Deposition Power #1:	60	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Ir	Time:		34/45min		Presput Power Film #2:	100	Time:	12min
Deposition Power #2:	100	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	2			Comments	Left window shutter is not working				
Total Sputter Time (all sample holders combined) Target #1	20min			Total Sputter Time (all sample holders) Target #2	19min				

Name/Date:	Shirin, 6.10.2011		Date:		Start Time		End Time	Load lock BP	
Process Gas (es)		Substrate: Si		Deposition Pressure (mT)				Chamber BP	8 6.3-7
Target Material #1	Ti	Time: 3min				Presput Power Film #1:		Time:	
Deposition Power #1:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Au	Time: 27 37s				Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	2			Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date: SAM BELL MAY 6 2011		Date: 5/6/2011	Start Time [illegible]	End Time		Load lock BP	1.3e[illegible]
Process Gas (es)	Argon	Substrate: Glass	Deposition Pressure (mT) 10	End Time		Chamber BP	2.4-7
Target Material #1	IR	Time: 3 min		Presput Power Film #1: 50W		Time:	2 min
Deposition Power #1:	50 W	Time:	Film Thickness (nm):		Deposition rate (Å/s)		
Target Material #2	IR	Time: 30 min		Presput Power Film #2: 100 W		Time:	1 min
Deposition Power #2:	100 W	Time:	Film Thickness (nm):		Deposition rate (Å/s)		
Number of Sample Holders With Substrates:	2		Comments				
Total Sputter Time (all sample holders combined) Target #1	1hr		Total Sputter Time (all sample holders) Target #2				

Name/Date: Yan Xie May 8. 2011		Date:	Start Time 6:30pm	End Time		Load lock BP	~~5.8x10-7~~ 1.2x10-6
Process Gas (es)	Ar	Substrate: GLASS	Deposition Pressure (mT)	10mT		Chamber BP	5.8x10-7
Target Material #1	TiW	Time: 16S		Presput Power Film #1:		Time:	2 min
Deposition Power #1:	50W	Time:	Film Thickness (nm):		Deposition rate (Å/s)		
Target Material #2	Au	Time: 2 min		Presput Power Film #2:		Time:	2 min
Deposition Power #2:	50W	Time:	Film Thickness (nm):		Deposition rate (Å/s)		
Number of Sample Holders With Substrates:	2		Comments				
Total Sputter Time (all sample holders combined) Target #1			Total Sputter Time (all sample holders) Target #2				

Name/Date: Sandeep (BR)		Date: 5/20/11	Start Time 11am	End Time		Load lock BP	2x10-6
Process Gas (es)	Ar/O2	Substrate: Si	Deposition Pressure (mT) 10			Chamber BP	1.8x10-7
Target Material #1	Ti	Time: 10 min		Presput Power Film #1: 90W		Time:	1 min
Deposition Power #1:	90	Time:	Film Thickness (nm):		Deposition rate (Å/s)		
Target Material #2	Ir	Time: 30 min		Presput Power Film #2: 100		Time:	5 min
Deposition Power #2:	100	Time:	Film Thickness (nm):		Deposition rate (Å/s)		
Number of Sample Holders With Substrates:	ONE		Comments				
Total Sputter Time (all sample holders combined) Target #1	10 min		Total Sputter Time (all sample holders) Target #2	30 min			

Name/Date: Raja Kumar Marthena		Date: 05/22/11	Start Time 1:45	End Time 3:15		Load lock BP	3.0x10-4
Process Gas (es)	Argon	Substrate: Si	Deposition Pressure (mT)	10mT		Chamber BP	3.3x10-7
Target Material #1	Pt	Time: 5 min 35 sec		Presput Power Film #1: 90		Time:	5 min [illegible]
Deposition Power #1:	90W	Time:	Film Thickness (nm):		Deposition rate (Å/s)		[illegible]
Target Material #2		Time:		Presput Power Film #2:		Time:	
Deposition Power #2:		Time:	Film Thickness (nm):		Deposition rate (Å/s)		
Number of Sample Holders With Substrates:	ONE		Comments				
Total Sputter Time (all sample holders combined) Target #1			Total Sputter Time (all sample holders) Target #2				

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date:	Sandeep (BR)	Date:	5/2/11	Start Time	11:30am	End Time		Load lock BP	2x10^-6
Process Gas (es)	Ar/10	Substrate:	Si	Deposition Pressure (mT)	10	End Time		Chamber BP	2x10^-7
Target Material #1	Ti	Time:		Presput Power Film #1:	90W	Time:	2min		
Deposition Power #1:	90 ~~100~~	Time:	10 min	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Ir	Time:	30 min	Presput Power Film #2:	100	Time:	5min		
Deposition Power #2:	100W	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	ONE	Comments							
Total Sputter Time (all sample holders combined) Target #1	10 min	Total Sputter Time (all sample holders) Target #2	30 min						

Window shutter NOT working

Name/Date:	ROHIT SHARMA	Date:	5/3/11	Start Time	11:30	End Time	1:30	Load lock BP	3.8x10^-6
Process Gas (es)	Ar/150	Substrate:	Si	Deposition Pressure (mT)				Chamber BP	4x10^-7
Target Material #1	Ti/Pt/Au	Time:	10/10/6 mins	Presput Power Film #1:		Time:	90/90/90W		
Deposition Power #1:	90/90/90	~~Time:~~ Process Pr	10/11/20mT	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:		Presput Power Film #2:		Time:			
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:		Comments							
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2							

Name/Date:	ROHIT SHARMA	Date:		Start Time		End Time		Load lock BP	5x10^-6
Process Gas (es)	Ar/150	Substrate:	Si	Deposition Pressure (mT)				Chamber BP	5.6x10^-7
Target Material #1	TiW	Time:	30 mins	Presput Power Film #1:		Time:	~~4~~ 45W		
Deposition Power #1:	45W	~~Time:~~ Pr.	5mT	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:		Presput Power Film #2:		Time:			
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:		Comments							
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2							

Name/Date:	Kiya Kumar Martha	Date:	05/04/11	Start Time	17:50	End Time		Load lock BP	4.1x10^-6
Process Gas (es)	Ar	Substrate:	Si	Deposition Pressure (mT)	-			Chamber BP	8.9x10^-7
Target Material #1	Pt	Time:	25 min 8s	Presput Power Film #1:		Time:			
Deposition Power #1:	90	Time: 3	5 min 33 sec	Film Thickness (nm):	~100nm	Deposition rate (Å/s)			
Target Material #2		Time:		Presput Power Film #2:		Time:			
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:		Comments							
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2							

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date: Srinivas Menon	Date: 04/06/11	Start Time: 12:30pm	End Time: 2:30pm	Load lock BP: 1.1x10⁻⁶
Process Gas (es): Ar, O₂	Substrate: Si	Deposition Pressure (mT)	End Time	Chamber BP: 3.2x10⁻⁷
Target Material #1: Ti	Time: 20	20mins (10+2)	Presput Power Film #1:	Time: 2
Deposition Power #1: 90W	Time:	Film Thickness (nm):	Deposition rate (Å/s)	
Target Material #2: ITO	Time: 44 (2+22) mins		Presput Power Film #2:	Time: 12 mins
Deposition Power #2: 100W	Time:	Film Thickness (nm):	Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments: Si		
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2		

Name/Date: Robert Hackendorn	Date: 4/12/11	Start Time	End Time	Load lock BP
Process Gas (es): Ar	Substrate:	Deposition Pressure (mT)		Chamber BP
Target Material #1: Pt	Time:		Presput Power Film #1:	Time:
Deposition Power #1: 90W	Time: ~17 sec.	Film Thickness (nm):	Deposition rate (Å/s)	
Target Material #2	Time:		Presput Power Film #2:	Time:
Deposition Power #2:	Time:	Film Thickness (nm):	Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments		
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2		

Name/Date: Yan Xie	Date: 4/22/11	Start Time: 4:00	End Time: 6:30	Load lock BP: 1.2x10⁻⁶
Process Gas (es): Ar	Substrate: Glass	Deposition Pressure (mT): 10 mT		Chamber BP: 5.8x10⁻⁷
Target Material #1: TiW	Time: 16 S		Presput Power Film #1:	Time: 2 min
Deposition Power #1: 50 W	Time:	Film Thickness (nm):	Deposition rate (Å/s)	
Target Material #2: Au	Time: 2 min		Presput Power Film #2:	Time: 2 min
Deposition Power #2: 50W	Time:	Film Thickness (nm):	Deposition rate (Å/s)	
Number of Sample Holders With Substrates: 2		Comments		
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2		

Name/Date: Richard Morrill	Date: 4/26/11	Start Time: 12:00pm	End Time	Load lock BP: 2.3x10⁻⁶
Process Gas (es): Ar	Substrate: GaSb	Deposition Pressure (mT): 10mT		Chamber BP: 5.1x10⁻⁷
Target Material #1: Ti	Time:		Presput Power Film #1: 45	Time: 2 min
Deposition Power #1: 45	Time: 2.5 min	Film Thickness (nm): 20 nm	Deposition rate (Å/s): est. [illegible]	
Target Material #2: Pt / Au	Time:		Presput Power Film #2: 45/45	Time: 2min/2min
Deposition Power #2: 45 / 45	Time: 3.5 min / 12 min	Film Thickness (nm): 30 nm / 200 nm	Deposition rate (Å/s)	est. 9 nm/min / 17 nm/min
Number of Sample Holders With Substrates:		Comments		
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2		

Comments: Increased pressure from 10 to 20 mT to create plasma on Ti and Au targets. I opened the shutter to create the plasma on the Pt target (and the pressure was increased from 10 to 20 mT)

TM Vacuum Sputter Deposition LOG

Name/Date:	Je-Min Yoo			Date:	3/2? '11	Start Time	2?:30	End Time		Load lock BP	6.?-?
Process Gas (es)	Ar	Substrate:	Si		Deposition Pressure (mT)			End Time		Chamber BP	?.8-7
Target Material #1	Ti	Time:	10	Gas: Ar 150 sccm			Presput Power Film #1:	90		Time:	2
Deposition Power #1:	90	Time:			Film Thickness (nm):		Deposition rate (Å/s)				
Target Material #2	Ir	Time:	45	Gas: Ar 100 O2 100			Presput Power Film #2:	100		Time:	20
Deposition Power #2:	100	Time:			Film Thickness (nm):		Deposition rate (Å/s)				
Number of Sample Holders With Substrates:	1				Comments						
Total Sputter Time (all sample holders combined) Target #1	10				Total Sputter Time (all sample holders) Target #2	45					

Name/Date:	Sandeep (BR)			Date:	3/31/11	Start Time	11:30am	End Time	1pm	Load lock BP	2x10-6
Process Gas (es)	Ar/O2	Substrate:	Si		Deposition Pressure (mT)					Chamber BP	1.8x10-7
Target Material #1	Ti	Time:	10				Presput Power Film #1:	90		Time:	2
Deposition Power #1:	90	Time:			Film Thickness (nm):		Deposition rate (Å/s)				
Target Material #2	Ir	Time:	45				Presput Power Film #2:	100		Time:	2 min
Deposition Power #2:	100	Time:			Film Thickness (nm):		Deposition rate (Å/s)				
Number of Sample Holders With Substrates:	ONE				Comments						
Total Sputter Time (all sample holders combined) Target #1					Total Sputter Time (all sample holders) Target #2						

Name/Date:	Srinivas			Date:	3/1/11	Start Time	11 AM	End Time	3Pm	Load lock BP	1x10-?
Process Gas (es)	Ar	Substrate:	Si		Deposition Pressure (mT)	10m?				Chamber BP	3.2x10-?
Target Material #1	Ti	Time:	10				Presput Power Film #1:	90		Time:	2 min
Deposition Power #1:	90	Time:			Film Thickness (nm):		Deposition rate (Å/s)				2.2 [illegible]
Target Material #2	Ir	Time:	25				Presput Power Film #2:	100		Time:	1.2 min.
Deposition Power #2:	100	Time:			Film Thickness (nm):		Deposition rate (Å/s)				
Number of Sample Holders With Substrates:					Comments						
Total Sputter Time (all sample holders combined) Target #1					Total Sputter Time (all sample holders) Target #2						

Name/Date:	Srinivas Merugu			Date:	4/4/11	Start Time	3 PM	End Time	5.15pm	Load lock BP	7.2x10-?
Process Gas (es)	Ar	Substrate:	Si piece		Deposition Pressure (mT)	10mT				Chamber BP	2.2x10-7
Target Material #1	Ti	Time:					Presput Power Film #1:			Time:	2 mins
Deposition Power #1:	90W	Time:	10 mins x2		Film Thickness (nm):		Deposition rate (Å/s)				
Target Material #2	Ir/Ru	Time:	25x2 min				Presput Power Film #2:			Time:	10 mins
Deposition Power #2:	100W	Time:			Film Thickness (nm):		Deposition rate (Å/s)				
Number of Sample Holders With Substrates:					Comments						
Total Sputter Time (all sample holders combined) Target #1					Total Sputter Time (all sample holders) Target #2						

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date:	Sandeep (BR)	Date:	3/23/11	Start Time	10:30am	End Time	12:15pm	Load lock BP	1.2×10^{-6}
Process Gas (es)	Ar/O_2	Substrate:	Si	Deposition Pressure (mT)		End Time		Chamber BP	1.9×10^{-7}
Target Material #1	Ti	Time:	10 min	Presput Power Film #1:	90	Time:	2		
Deposition Power #1:	90	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Ir	Time:	45 min	Presput Power Film #2:	100	Time:	2		
Deposition Power #2:	100	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	ONE	Comments							
Total Sputter Time (all sample holders combined) Target #1	10	Total Sputter Time (all sample holders) Target #2	45						

Name/Date:	Rohit Sharma	Date:	3/23/11	Start Time	~~3:00~~ 4:00	End Time	5:30	Load lock BP	5.1×10^{-6}
Process Gas (es)	Ar	Substrate:	Si	Deposition Pressure (mT)	—	—		Chamber BP	3.7×10^{-7}
Target Material #1	Ti	Time:	10 min	Presput Power Film #1:		Time:	2 min		
Deposition Power #1:	90W	Time: Pr	10mT	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Pt/Au	Time:	10/6 min	Presput Power Film #2:		Time:	2/2 min		
Deposition Power #2:	90/90	Time: Pr	11/20mT	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:		Comments							
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2							

Name/Date:	Rohit Sharma	Date:	3/24/11	Start Time	9:00	End Time	10:30	Load lock BP	5.3×10^{-6}
Process Gas (es)	Ar	Substrate:	Si	Deposition Pressure (mT)				Chamber BP	8.4×10^{-7}
Target Material #1	TiW	Time:	~~2~~ 5 min	Presput Power Film #1:		Time:	2 min		
Deposition Power #1:	450W	Time: Pr	5mT	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:		Presput Power Film #2:		Time:			
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:		Comments							
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2		6.7×10^{-7}					

Name/Date:	Xianzong Xie	Date:	3/24/11	Start Time	11:00	End Time	2:30	Load lock BP	
Process Gas (es)	Ar	Substrate:	quartz	Deposition Pressure (mT)				Chamber BP	
Target Material #1	Ti	Time:	10 min	Presput Power Film #1:		Time:	2 min		
Deposition Power #1:	90W	Time: Pr	10mT	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Pt/Au	Time: Pr	11/10mTo	Presput Power Film #2:		Time:	2 min		
Deposition Power #2:	90W	Time:	10/6 min	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:		Comments							
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2							

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date:	[illegible] Xiong / 03-11-2011			Date:	03-11-2011	Start Time	2:27pm	End Time	3:24	Load lock BP	
Process Gas (es)	Ar	Substrate:	Glass	Deposition Pressure (mT)	[illegible]	End Time		Chamber BP	4.3×10[illegible]
Target Material #1	Ti	Time:	1min		Presput Power Film #1:			Time:	
Deposition Power #1:	100w	Time:		Film Thickness (nm):	~10nm	Deposition rate (Å/s)		100Å/s	
Target Material #2	Au	Time:	2min		Presput Power Film #2:			Time:	
Deposition Power #2:	50w	Time:		Film Thickness (nm):	~40nm	Deposition rate (Å/s)		200Å/s	
Number of Sample Holders With Substrates:	1			Comments					
Total Sputter Time (all sample holders combined) Target #1	1min			Total Sputter Time (all sample holders) Target #2	2min				

Name/Date:	[illegible] Xiong			Date:	03/15/2011	Start Time	8:13pm	End Time	9:30	Load lock BP	
Process Gas (es)	Ar	Substrate:	SiO2	Deposition Pressure (mT)				Chamber BP	7.6×10[illegible]
Target Material #1	Ti	Time:			Presput Power Film #1:			Time:	
Deposition Power #1:	200w	Time:	2min	Film Thickness (nm):	~~225~~ 10nm	Deposition rate (Å/s)		1Å/s	
Target Material #2	Au	Time:			Presput Power Film #2:			Time:	
Deposition Power #2:	200w	Time:	3min	Film Thickness (nm):	~225nm	Deposition rate (Å/s)	~~78~~	12.5Å/s	
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1	1min			Total Sputter Time (all sample holders) Target #2	3min				

Name/Date:	Sandeep (BR)			Date:	3/17/11	Start Time	2pm	End Time	3.30pm	Load lock BP	8×10[illegible] Torr
Process Gas (es)	Ar/O2	Substrate:		Deposition Pressure (mT)				Chamber BP	2×10[illegible]
Target Material #1	Ti	Time:	20 min		Presput Power Film #1:	90		Time:	2
Deposition Power #1:	90	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Ir	Time:	45		Presput Power Film #2:	100		Time:	~~65~~ 2 min
Deposition Power #2:	100	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	One			Comments					
Total Sputter Time (all sample holders combined) Target #1	10			Total Sputter Time (all sample holders) Target #2	45				

Name/Date:	Layne Williams			Date:	3/18/11	Start Time	3:00	End Time		Load lock BP	9×10[illegible]
Process Gas (es)		Substrate:	Si/Glass	Deposition Pressure (mT)	10			Chamber BP	2.6×10[illegible]
Target Material #1	Ti	~~Time:~~ Gas	Ar/150 sccm		Presput Power Film #1:	90		Time:	2
Deposition Power #1:	90	Time:	10	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	IrOx	~~Time:~~ Gas	Ar/100, O2/100		Presput Power Film #2:	100		Time:	10 pre / 10 p[illegible]
Deposition Power #2:	100	Time:	45	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	1			Comments					
Total Sputter Time (all sample holders combined) Target #1	10			Total Sputter Time (all sample holders) Target #2	45				

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date: Layne Williams		Date: 3/8/11	Start Time 2:00	End Time 5:30	Load lock BP 1.1x-6
~~Process Gas (es)~~	Substrate: Si/Glass	Deposition Pressure (mT) 10		~~End Time~~ →	Chamber BP 2.5x-7
Target Material #1: Ti	~~Time:~~ ~~Gas x2~~	Ar/150 sccm		Presput Power Film #1: 90	Time: 2 min
Deposition Power #1: 90	~~Time:~~ Time	10 min	Film Thickness (nm):	Deposition rate (Å/s)	
Target Material #2: IrOx	~~Time:~~ Gas	Ar/100, O2/100 sccm		Presput Power Film #2:	Time: 10 min/pre & post
Deposition Power #2: 1000	Time: ~~[illegible]~~	45	Film Thickness (nm):	Deposition rate (Å/s)	
Number of Sample Holders With Substrates: 2		Comments			
Total Sputter Time (all sample holders combined) Target #1		20	Total Sputter Time (all sample holders) Target #2	90	

Name/Date: Layne Williams		Date: 3/9/11	Start Time 11:45	End Time	Load lock BP 9.7x-7
~~Process Gas (es)~~	Substrate: Si/Glass	Deposition Pressure (mT) 10			Chamber BP 2x10-7
Target Material #1: Ti	~~Time:~~ Gas	Ar/150 sccm		Presput Power Film #1: 90	Time: 2
Deposition Power #1: 90	Time:	10	Film Thickness (nm):	Deposition rate (Å/s)	
Target Material #2: IrOx	~~Time:~~ Gas	Ar/100, O2 100 sccm		Presput Power Film #2: 100	Time: 10/10 pre & post
Deposition Power #2: 100	Time:	45	Film Thickness (nm):	Deposition rate (Å/s)	
Number of Sample Holders With Substrates: 2		Comments			
Total Sputter Time (all sample holders combined) Target #1		20	Total Sputter Time (all sample holders) Target #2	90	

Name/Date: Jung Woo Park		Date: 3/16/11	Start Time 4:00pm	End Time 4:50pm	Load lock BP 3.5E-6
Process Gas (es): Ar	Substrate: Si	Deposition Pressure (mT) 10			Chamber BP ~~2E-7~~ 5.5E-7
Target Material #1: Ti	Time: 2 m			Presput Power Film #1: 45	Time:
Deposition Power #1: 45	Time: 2 m		Film Thickness (nm): 20	Deposition rate (Å/s)	
Target Material #2: Au	Time:			Presput Power Film #2: 50	Time:
Deposition Power #2: 50	Time: 10 m		Film Thickness (nm): 200	Deposition rate (Å/s)	
Number of Sample Holders With Substrates: 2		Comments			
Total Sputter Time (all sample holders combined) Target #1			Total Sputter Time (all sample holders) Target #2		

Name/Date: Trevor Xray		Date: 03/23	Start Time 8:40	End Time 10:20	Load lock BP 1.8x10-6
Process Gas (es): Ar	Substrate: PDMS	Deposition Pressure (mT)			Chamber BP 1.8x10-7
Target Material #1: Ti	Time:			Presput Power Film #1:	Time: 1 min
Deposition Power #1: 50W	Time:	2 min	Film Thickness (nm): ~5nm	Deposition rate (Å/s)	
Target Material #2: Au	Time:			Presput Power Film #2:	Time: 1 min
Deposition Power #2: 250W	Time:	10 min	Film Thickness (nm): ~100nm	Deposition rate (Å/s)	10 nm/min
Number of Sample Holders With Substrates: 1		Comments			
Total Sputter Time (all sample holders combined) Target #1		2 min	Total Sputter Time (all sample holders) Target #2	10 min	

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date:	Rohit Sharma	Date:	02/28/11	Start Time	3:45	End Time	5:30	Load lock BP	3.7x10-6
Process Gas (es)	Ar (150)	Substrate:	Si	Deposition Pressure (mT)		End Time		Chamber BP	6.0x10-7
Target Material #1	Ti	Time:	10mins	Presput Power Film #1:		Time:	5mins		
Deposition Power #1:	90W	~~Time:~~ Pr.	10mT	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Au/Pt	Time:	6min/10min	Presput Power Film #2:		Time:	2/2min		
Deposition Power #2:	90/90W	~~Time:~~ Pr	20/10mT	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:		Comments							
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2							

Name/Date:	Rohit Sharma	Date:	02/8/~~[illegible]~~	Start Time	6:30	End Time	7:30	Load lock BP	8.8x10-6
Process Gas (es)	Ar (150)	Substrate:	Si	Deposition Pressure (mT)				Chamber BP	
Target Material #1	TiW	Time:	30mins	Presput Power Film #1:		Time:	2min		
Deposition Power #1:	45W	~~Time:~~ Pr	5mT	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:		Presput Power Film #2:		Time:			
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:		Comments							
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2							

Name/Date:	Layne Williams	Date:	3/1/11	Start Time	12:00	End Time	5:20	Load lock BP	8.2x-7
Process Gas (es)		Substrate:	Si/Glass	Deposition Pressure (mT)	10mT			Chamber BP	2.5x-7
Target Material #1	Ti	~~Time:~~ Gas	Ar 150 sccm	Presput Power Film #1:	90	Time:	2		
Deposition Power #1:	90	Time:	10 min	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	IrOx	~~Time:~~ Gas	Ar, 100, O2 100 sccm	Presput Power Film #2:	100	Time:	10 pre/10 post		
Deposition Power #2:	100	Time:	45min	~~40min~~ Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	2	Comments							
Total Sputter Time (all sample holders combined) Target #1	20	Total Sputter Time (all sample holders) Target #2	90						

Name/Date:	Iridib Ghosh	Date:	3/4/2011	Start Time	1:50pm	End Time	2:30pm	Load lock BP	1.2x10-6
Process Gas (es)	Ar	Substrate:	Glass	Deposition Pressure (mT)	10mT			Chamber BP	5.8x10-7
Target Material #1	Ti/W	Time:	16S	Presput Power Film #1:		Time:	2 min		
Deposition Power #1:	50W	Time:		Film Thickness (nm):	2-3nm	Deposition rate (Å/s)	6-8 nm/min		
Target Material #2	Au	Time:	2min	Presput Power Film #2:		Time:	2 min		
Deposition Power #2:	50W	Time:		Film Thickness (nm):	40nm	Deposition rate (Å/s)	20 nm/min		
Number of Sample Holders With Substrates:	2	Comments							
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2							

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date:	Layne Williams	Date:	1/28/11	Start Time	same	End Time	4:30	Load lock BP	same
Process Gas (es)		Substrate:	Glass	Deposition Pressure (mT)	10	End Time		Chamber BP	same
Target Material #1	Ti	~~Time:~~ Gas	Ar 150 sccm			Presput Power Film #1:	90	Time:	X
Deposition Power #1:	90	Time:	20	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Au	~~Time:~~ Gas	Ar 150 sccm			Presput Power Film #2:	45	Time:	2
Deposition Power #2:	45	Time:	10	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments	Rotation not good for Au deposition, Chuck 6				
Total Sputter Time (all sample holders combined) Target #1			20	Total Sputter Time (all sample holders) Target #2				10	

Name/Date:	Layne Williams	Date:	2/17/11	Start Time	9:30	End Time		Load lock BP	1.4x-6
Process Gas (es)		Substrate:	Si	Deposition Pressure (mT)	10			Chamber BP	4.5x-7
Target Material #1	Ti	~~Time:~~ Gas	Ar 150 sccm			Presput Power Film #1:	90	Time:	~~2~~ 5
Deposition Power #1:	90	Time:	10	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Ir Ox	~~Time:~~ Gas	Ar 100, O_2 100 sccm			Presput Power Film #2:	100	Time:	10 / 15
Deposition Power #2:	100	Time:	45	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:			2	Comments	Cryo needs regeneration				
Total Sputter Time (all sample holders combined) Target #1			20	Total Sputter Time (all sample holders) Target #2				90	

Name/Date:	Abhijit Mandal 2/17/2011	Date:	2/17/2011	Start Time	2:30pm	End Time	4:00pm	Load lock BP	2.9x10-7
Process Gas (es)		Substrate:	Polycarbonate	Deposition Pressure (mT)	10			Chamber BP	
Target Material #1	Ti	Time:	2 min	Ar - 150 sccm O_2 = 100 sccm		Presput Power Film #1:		Time:	2 min
Deposition Power #1:	45W	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Au	Time:	5 min	Ar - 150 sccm		Presput Power Film #2:		Time:	2 min
Deposition Power #2:	50W	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:			2	Comments					
Total Sputter Time (all sample holders combined) Target #1			4 min	Total Sputter Time (all sample holders) Target #2				10 min	

Name/Date:	ROHIT SHARMA	Date:	2/25/11	Start Time	1:30	End Time	4:30	Load lock BP	3x10-6
Process Gas (es)	Ar (150)	Substrate:	Si	Deposition Pressure (mT)				Chamber BP	3.6x10-7
Target Material #1	Ti/Pt/Au	Time:	10/10/6 mins			Presput Power Film #1:		Time:	5/2/2 mins
Deposition Power #1:	90/90/90	~~Time:~~ Pressure	10/11/20mT	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	TiW	Time:	8 5 mins			Presput Power Film #2:		Time:	2 mins
Deposition Power #2:	45W	~~Time:~~ Pr.	5mT	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date:	Layne Williams		Date:	1/18/11	Start Time 3:00	End Time	Load lock BP	9.4x-7
Process Gas (es)		Substrate:	Si	Deposition Pressure (mT) 10		End Time	Chamber BP	3.6x-7
Target Material #1	Ti	~~Time:~~ Gas	Ar 150 sccm		Presput Power Film #1:		Time:	2
Deposition Power #1:	90W	Time:	10	Film Thickness (nm):		Deposition rate (Å/s)		
Target Material #2	IrOx	Time:	Ar 100 sccm, O_2 100 sccm		Presput Power Film #2:		Time:	10
Deposition Power #2:	100W	Time:	50	Film Thickness (nm):		Deposition rate (Å/s)		
Number of Sample Holders With Substrates:			1	Comments				
Total Sputter Time (all sample holders combined) Target #1			10	Total Sputter Time (all sample holders) Target #2			50	

Name/Date:	Jian Xie		Date:	1/18/11	Start Time 6:00	End Time	Load lock BP	9.4×10^{-7}
Process Gas (es)		Substrate:	Pyrene	Deposition Pressure (mT) 10			Chamber BP	3.6×10^{-7}
Target Material #1	Au	~~Time:~~ Gas	Ar 150 sccm		Presput Power Film #1:		Time:	2
Deposition Power #1:	50W	Time:	5 min	Film Thickness (nm):		Deposition rate (Å/s)		
Target Material #2		Time:			Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)		
Number of Sample Holders With Substrates:			3	Comments				
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2				

Name/Date:	Jian Xie		Date:	1/19/11	Start Time 6:00	End Time	Load lock BP	9.4×10^{-7}
Process Gas (es)		Substrate:	Si	Deposition Pressure (mT) 10			Chamber BP	3.6×10^{-7}
Target Material #1	Cr	~~Time:~~ Gas	Ar 150 sccm		Presput Power Film #1:		Time:	2
Deposition Power #1:	150W	Time:	15 min	Film Thickness (nm):		Deposition rate (Å/s)		
Target Material #2		Time:			Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)		
Number of Sample Holders With Substrates:			3	Comments				
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2				

Name/Date:	Layne Williams		Date:	1/28/11	Start Time 11:30	End Time 4:30	Load lock BP	6x-7
Process Gas (es)		Substrate:	Si	Deposition Pressure (mT)	10		Chamber BP	3.2x-7
Target Material #1	Ti	~~Time:~~ Gas	Ar 150 sccm		Presput Power Film #1: 90		Time:	2
Deposition Power #1:	90	Time:	10	Film Thickness (nm):		Deposition rate (Å/s)		
Target Material #2	IrOx	~~Time:~~ Gas	Ar 100, O_2 100 sccm		Presput Power Film #2: 100		Time:	10/10
Deposition Power #2:	100	Time:	45	Film Thickness (nm):		Deposition rate (Å/s)		
Number of Sample Holders With Substrates:			1	Comments				
Total Sputter Time (all sample holders combined) Target #1			10	Total Sputter Time (all sample holders) Target #2			45	

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date:	Layne Williams		Date:	1/15/11	Start Time	5:00	End Time	8:30	Load lock BP: 9x-7
Process Gas (es)		Substrate:		Deposition Pressure (mT)	18		End Time		Chamber BP: 3.9x-7
Target Material #1	IrOx	~~Time:~~ Gas	Ar 100 O2 100 sccm		Presput Power Film #1:	100W			Time: 10/10
Deposition Power #1:	100W	Time:	60 min	Film Thickness (nm):	1100	Deposition rate (Å/s)			
Target Material #2	Cr	~~Time:~~ Gas	Ar 150		Presput Power Film #2:	50W			Time: 2 min
Deposition Power #2:	50W	Time:	3 min	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:			4	Comments					
Total Sputter Time (all sample holders combined) Target #1			60 min	Total Sputter Time (all sample holders) Target #2				9 min	

Name/Date:	same		Date:	same	Start Time	same	End Time		Load lock BP: same
Process Gas (es)		Substrate:		Deposition Pressure (mT)	18				Chamber BP: same
Target Material #1	Au	~~Time:~~ Gas	Ar 150		Presput Power Film #1:	50W			Time: 2
Deposition Power #1:	50W	Time:	5 min	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:			Presput Power Film #2:				Time:
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:			3	Comments					
Total Sputter Time (all sample holders combined) Target #1			15 min	Total Sputter Time (all sample holders) Target #2					

Name/Date:	Layne Williams		Date:	1/17/11	Start Time	11:30	End Time		Load lock BP: 7.9x-7
Process Gas (es)		Substrate:	Si	Deposition Pressure (mT)		10			Chamber BP: 3.6x-7
Target Material #1	Ti	~~Time:~~ Gas	Ar 150 sccm		Presput Power Film #1:	90W			Time: 2
Deposition Power #1:	90 W	Time:	10/15 min	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	IrOx	~~Time:~~ Gas	Ar 100, O2 100 sccm		Presput Power Film #2:	100W			Time: 10
Deposition Power #2:	100 W	Time:	55 min	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1			25 min	Total Sputter Time (all sample holders) Target #2				55	

Name/Date:	Layne Williams		Date:	1/17/11	Start Time	same	End Time		Load lock BP:
Process Gas (es)		Substrate:		Deposition Pressure (mT)	11				Chamber BP:
Target Material #1	Pt	~~Time:~~ Gas	Ar 150 sccm		Presput Power Film #1:	90			Time: 2
Deposition Power #1:	90	Time:	15	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:			Presput Power Film #2:				Time:
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Comments:

All one deposition run

TM Vacuum Sputter Deposition LOG

Name/Date:	[illegible]an Xie		Date:	1/12/11	Start Time	6:30pm	End Time	10:30 pm	Load lock BP	5.9x10-7
Process Gas (es)	Ar	Substrate:	SiN	Deposition Pressure (mT)	10	End Time		Chamber BP	3.6x10-7
Target Material #1	Cr	Time:			Presput Power Film #1:	50W		Time:	2 min
Deposition Power #1:	50W	Time:	2 min	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Au	Time:			Presput Power Film #2:	50W		Time:	2 min
Deposition Power #2:	50W	Time:	2 min	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:			2	Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date:	Layne Williams		Date:	1/13/1[illegible]	Start Time	2:30	End Time	Load lock BP	1.2x-6
Process Gas (es)		Substrate:	Si	Deposition Pressure (mT)	10			Chamber BP	3.8x-7
Target Material #1	~~[illegible]~~ Ti	~~Time:~~ Gas	Ar /150		Presput Power Film #1:	90		Time:	2
Deposition Power #1:	90	Time:	10 min	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	IrOx	~~Time:~~ Gas	Ar/150, O2/150		Presput Power Film #2:	100		Time:	10
Deposition Power #2:	100	Time:	70	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date:	Layne Williams		Date:	1/13/1[illegible]	Start Time	2:30	End Time	Load lock BP	same
Process Gas (es)	Ar	Substrate:	Glass	Deposition Pressure (mT)	10			Chamber BP	same
Target Material #1	Ir	Time:			Presput Power Film #1:	100W		Time:	2
Deposition Power #1:	100W	Time:	10	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:			Presput Power Film #2:			Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date:	Layne Williams		Date:	1/15/1[illegible]	Start Time	12:00	End Time	4:30	Load lock BP	9.7x-7
Process Gas (es)		Substrate:	Si	Deposition Pressure (mT)	10			Chamber BP	3.8x-7
Target Material #1	IrOx	~~Time:~~ Gas	Ar 100, O2 100 sccm		Presput Power Film #1:	100		Time:	10 /10
Deposition Power #1:	100 W	Time:	50 min	Film Thickness (nm):	800	Deposition rate (Å/s)			
Target Material #2	Ti	~~Time:~~	Ar 150		Presput Power Film #2:	90W		Time:	2
Deposition Power #2:	90W	Time:	15 min	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:			3	Comments	Had to				
Total Sputter Time (all sample holders combined) Target #1			50 min	Total Sputter Time (all sample holders) Target #2			30 min		
Comments:									

Pt, 90W, Ar 150, 2 min presputter, 15 min sputter 2x total time = 30 min

All one deposition run

TM Vacuum Sputter Deposition LOG

Name/Date:	Layne Williams	Date:	1/12/11	Start Time	9:00	End Time	1:30	Load lock BP	5×-7
Process Gas (es)	Ar	Substrate:	Si	Deposition Pressure (mT)		End Time		Chamber BP	3.4×-7
Target Material #1	Ti	~~Time:~~ Gas	Ar/150 sccm	10 mt		Presput Power Film #1:	90W	Time:	2
Deposition Power #1:	90	Time:	15 min	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Pt	~~Time:~~ Gas	Ar/150 sccm	11 mt		Presput Power Film #2:	90W	Time:	2
Deposition Power #2:	90	Time:	15 min	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	2			Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					
Name/Date:	Layne Williams	Date:	1/12/11	Start Time	9:00	End Time	1:30	Load lock BP	same
Process Gas (es)	Ar	Substrate:	Glass	Deposition Pressure (mT)				Chamber BP	same
Target Material #1	Ti/W	Time:				Presput Power Film #1:	~~100W~~ 45	Time:	2
Deposition Power #1:	45 ~~100W~~	Time:	30 min	Film Thickness (nm):	190	Deposition rate (Å/s)		≈6.3 nm/min	
Target Material #2	Au	Time:				Presput Power Film #2:	90	Time:	2
Deposition Power #2:	90	Time:	10	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	2			Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					
Name/Date:	Layne Williams	Date:	1/12/11	Start Time	1:30	End Time		Load lock BP	2×-6
Process Gas (es)		Substrate:	Si	Deposition Pressure (mT)	10			Chamber BP	3×-7
Target Material #1	Ti	~~Time:~~ Gas	Ar/150 sccm			Presput Power Film #1:	90W	Time:	2
Deposition Power #1:	90W	Time:	15 min	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Ti/W	~~Time:~~ Gas	Ar/150 sccm			Presput Power Film #2:	~~90W~~ 45	Time:	2
Deposition Power #2:	45	Time:	15 min	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					
Name/Date:	Layne Williams	Date:	1/12/11	Start Time	1:30	End Time		Load lock BP	same
Process Gas (es)		Substrate:	Si	Deposition Pressure (mT)				Chamber BP	same
Target Material #1	IrOx	~~Time:~~ Gas	Ar/100, O_2/150 sccm			Presput Power Film #1:	100	Time:	5/10
Deposition Power #1:	100 W	Time: 20 min /	35 min	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Ir	~~Time:~~ Gas	Ar/150 sccm			Presput Power Film #2:	100	Time:	5 min
Deposition Power #2:	100 W	Time: 10 min		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments	Ir deposition with pulsed DC				
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					
Comments:									

Cr, Ar/150 sccm, 10 mt, 100 W, 2 min presputter, 10 min dep

(First two entries:) All one deposition run

(Last two entries:) All one deposition run

TM Vacuum Sputter Deposition LOG

Name/Date:	Layne Williams	Date:	12/23	Start Time	10:00	End Time	
Load lock BP	—						
Process Gas (es)		Substrate:	Si	Deposition Pressure (mT)	10/11	End Time	
Chamber BP	2.7x-7						
Target Material #1	Ti	~~Time:~~ Gas	Ar/150 sccm	Presput Power Film #1:	90	Time:	5
Deposition Power #1:	90	Time:	10	Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	IrOx	~~Time:~~ Gas	Ar/100, O_2/100 sccm	Presput Power Film #2:	100	Time:	20/10 min per sputter
Deposition Power #2:	100	Time:	40	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:	1	Comments	Loaded directly in main chamber – transfer not working				
Total Sputter Time (all sample holders combined) Target #1	10	Total Sputter Time (all sample holders) Target #2	40				

Name/Date:	Layne Williams	Date:	1/10/11	Start Time	1:00	End Time	
Load lock BP	1.4x-6						
Process Gas (es)	~~Ti~~	Substrate:	Si	Deposition Pressure (mT)	10		
Chamber BP	3.8x-7						
Target Material #1	Ti	~~Time:~~ Gas	Ar/150 sccm	Presput Power Film #1:	90	Time:	2
Deposition Power #1:	90	Time:	10	Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	IrOx	~~Time:~~ Gas	Ar/100, O_2/100 sccm	Presput Power Film #2:	100	Time:	10/10
Deposition Power #2:	100	Time:	40	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:	1	Comments					
Total Sputter Time (all sample holders combined) Target #1	10	Total Sputter Time (all sample holders) Target #2	40				

Name/Date:	Layne Williams	Date:	1/10/11	Start Time	1:00	End Time	
Load lock BP	same						
Process Gas (es)	Ar/150 sccm	Substrate:	Glass	Deposition Pressure (mT)			
Chamber BP	Same						
Target Material #1	Ti	~~Time:~~ Pressure	10 mt	Presput Power Film #1:	90	Time:	2
Deposition Power #1:	90	Time:	10 min	Film Thickness (nm):	66	Deposition rate ~~(Å/s)~~ nm/min	6.6 nm/min
Target Material #2	Pt	~~Time:~~ Pressure	11 mt	Presput Power Film #2:	90	Time:	2
Deposition Power #2:	90	Time:	20 min	Film Thickness (nm):	330	Deposition rate (Å/s)	≈16 nm/min
Number of Sample Holders With Substrates:	2	Comments					
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Name/Date:	Layne Williams	Date:	1/10/11	Start Time		End Time	
Load lock BP	same						
Process Gas (es)	Ar/O_2	Substrate:	Glass	Deposition Pressure (mT)			
Chamber BP	same						
Target Material #1	IrOx	~~Time:~~ Gas	Ar/100, O_2/100 sccm	Presput Power Film #1:	100W	Time:	10/10
Deposition Power #1:	100W	Time:	~~10~~ 10 min	Film Thickness (nm):	120	Deposition rate (Å/s)	≈13 nm/min
Target Material #2		Time:		Presput Power Film #2:		Time:	≈
Deposition Power #2:		Time:	1	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments					
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Comments:

~~all one deposition run~~

ALL ONE DEPOSITION RUN

TM Vacuum Sputter Deposition LOG

Name/Date:	Rohit Sharma		Date:	12/20	Start Time	12:20	End Time	3:30	Load lock BP	3.3x10-6
Process Gas (es)	Ar/100	Substrate:	Si	Deposition Pressure (mT)			End Time		Chamber BP	8.0x10-7
Target Material #1	Ti/Pt	Time:	10/12 mins		Presput Power Film #1:				Time:	2/2 mins
Deposition Power #1:	90/90 W	~~Time:~~ Pr.	10/11 mT	Film Thickness (nm):		Deposition rate (Å/s)				
Target Material #2	TiW/Pt	Time:	52/31 mins		Presput Power Film #2:				Time:	2/1 mins
Deposition Power #2:	45/90 W	~~Time:~~ Pr.	5/11 mT	Film Thickness (nm):		Deposition rate (Å/s)				
Number of Sample Holders With Substrates:				Comments						
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2						

Name/Date:	Layne Williams		Date:	12/21	Start Time	12:30	End Time	4:00	Load lock BP	1.2x-6
Process Gas (es)		Substrate:	Si	Deposition Pressure (mT)		10/11			Chamber BP	3.8x-7
Target Material #1	Ti	~~Time:~~ Gas	Ar/150 sccm		Presput Power Film #1:	90			Time:	2
Deposition Power #1:	90	Time:	10	Film Thickness (nm):	~100 nm	Deposition rate (Å/s)	≈ 10 nm/min			
Target Material #2	Pt	~~Time:~~ Gas	Ar/150 sccm		Presput Power Film #2:	90			Time:	2
Deposition Power #2:	90	Time:	14	Film Thickness (nm):	≈ 200	Deposition rate (Å/s)				
Number of Sample Holders With Substrates:	2			Comments						
Total Sputter Time (all sample holders combined) Target #1	20			Total Sputter Time (all sample holders) Target #2	30					

Name/Date:	Nzong Xie		Date:	12/22	Start Time	9:30	End Time	11:00	Load lock BP	3.8x10-7
Process Gas (es)	Ar	Substrate:	Quartz	Deposition Pressure (mT)					Chamber BP	9.4x10-7
Target Material #1	Ti	Time:	10 min		Presput Power Film #1:				Time:	2 min
Deposition Power #1:	90 W	~~Time:~~ Presss	10 mTorr	Film Thickness (nm):		Deposition rate (Å/s)				
Target Material #2	Pt/Au	Time:	10/8 min		Presput Power Film #2:				Time:	2/2 min
Deposition Power #2:	90/90	~~Time:~~ Pre	10/10 mTorr	Film Thickness (nm):		Deposition rate (Å/s)				
Number of Sample Holders With Substrates:				Comments						
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2						

Name/Date:	Layne Williams		Date:	12/22	Start Time	11:45	End Time		Load lock BP	5x-7
Process Gas (es)		Substrate:	Si	Deposition Pressure (mT)		10			Chamber BP	3.2x-7
Target Material #1	Ti	~~Time:~~ Gas	Ar/150 sccm		Presput Power Film #1:	90			Time:	2
Deposition Power #1:	90	Time:	10	Film Thickness (nm):	180 nm	Deposition rate (Å/s)				
Target Material #2	IrOx	~~Time:~~ Gas	Ar/100, O_2/100 sccm		Presput Power Film #2:				Time:	~~15~~ 15
Deposition Power #2:	100	Time:	40	Film Thickness (nm):	1000	Deposition rate (Å/s)				
Number of Sample Holders With Substrates:	1			Comments	Post-sputter Ir for 10 min					
Total Sputter Time (all sample holders combined) Target #1	10			Total Sputter Time (all sample holders) Target #2	40					

Comments: Could not remove sample from chamber - transfer arm would not engage

TM Vacuum Sputter Deposition LOG

Name/Date: Raja Kumar Manthena		Date: 12/10/2010	Start Time 3:10	End Time 3:55	Load lock BP 9.4x10^-6
Process Gas (es) Ar	Substrate:	Deposition Pressure (mT)		End Time	Chamber BP 4.8x10^-7
Target Material #1 Pt	Time: 45 sec		Presput Power Film #1:		Time: 60 seconds
Deposition Power #1:	Time:	Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	Time:		Presput Power Film #2:		Time:
Deposition Power #2:	Time:	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments			
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2			

Name/Date: Wenzhong Xie		Date: 12/13/2010	Start Time 11:00	End Time 12:00	Load lock BP 3x10^-7
Process Gas (es) Ar	Substrate: Fused Silica	Deposition Pressure (mT)			Chamber BP 5.5x10^-7
Target Material #1 Ti	Time: 80 min		Presput Power Film #1:		Time: 2 min
Deposition Power #1: 90 w	Time: Pressure 10 mT	Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2 Pt/Au	Time: 10/8 min		Presput Power Film #2:		Time:
Deposition Power #2: 90/90 w	Time: pre 11/10 mT	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments			
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2			

Name/Date: Layne Williams		Date: 12/14/10	Start Time 1:45	End Time 5:30	Load lock BP 1.2x^-6
Process Gas (es) Ar, O2	Substrate: ~~Si~~ Si	Deposition Pressure (mT)	10		Chamber BP 3.1x^-7
Target Material #1 Ti	~~Time:~~ Gas Ar/150 sccm		Presput Power Film #1: 90		Time: ~~10~~ 2
Deposition Power #1: 90	Time: 10	Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2 IrOx	~~Time:~~ Gas Ar/100, O2/100 sccm		Presput Power Film #2: 100		Time: 12
Deposition Power #2: 100	Time: 40	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates: 1		Comments: Took a long time to pump chamber from 4.1 to 3.1x^-7			
Total Sputter Time (all sample holders combined) Target #1: 10		Total Sputter Time (all sample holders) Target #2: 40			

Name/Date: Wenzhong Xie		Date: 12/17/2010	Start Time 9:30	End Time 11:00	Load lock BP 7x10^-7
Process Gas (es) Ar	Substrate: Si	Deposition Pressure (mT)			Chamber BP 3x10^-7
Target Material #1 Ti	Time: 10 min		Presput Power Film #1:		Time: 2 min
Deposition Power #1: 90 W	Time: press 10 mT	Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2 Pt/Au	Time: 10/8 min		Presput Power Film #2:		Time:
Deposition Power #2: 90/90	Time: press 11/10 mT	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments			
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2			

Comments:

TM Vacuum Sputter Deposition LOG

Field	Value	Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Rohit Sharma			Date:	12/06/10	Start Time	2:00	End Time	5:30
Process Gas (es)	Ar (100)	Substrate:	Si					Load lock BP	3.1×10^{-6}
Target Material #1	Ti	Time:		Deposition Pressure (mT)		End Time		Chamber BP	4.1×10^{-7}
Deposition Power #1:	90	Time:	[illegible]	10 mTorr / 10 mT	Film Thickness (nm):	Presput Power Film #1:		Time:	2/2 min
Target Material #2	[illegible]	Time:				Deposition rate (Å/s)			
Deposition Power #2:	[illegible]	Time:	[illegible]	10/6 mm 11/2 mT	Film Thickness (nm):	Presput Power Film #2:		Time:	2/2 min
Number of Sample Holders With Substrates:				Comments		Deposition rate (Å/s)			
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Field	Value	Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Rohit Sharma			Date:	12/09/10	Start Time	10:00	End Time	11:15
Process Gas (es)	Ar (100)	Substrate:	Si	Deposition Pressure (mT)				Load lock BP	3.3×10^{-6}
Target Material #1	TiW	Time:	30 mins					Chamber BP	4.2×10^{-7}
Deposition Power #1:	4 kW	Time:	Pressure 3 mT	Film Thickness (nm):		Presput Power Film #1:		Time:	2 min
Target Material #2		Time:				Deposition rate (Å/s)			
Deposition Power #2:		Time:		Film Thickness (nm):		Presput Power Film #2:		Time:	
Number of Sample Holders With Substrates:				Comments		Deposition rate (Å/s)			
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Field	Value	Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	RAJA KUMAR MANTHENA			Date:	12/10/10	Start Time	11:05	End Time	12:00
Process Gas (es)	Ar	Substrate:	Quartz	Deposition Pressure (mT)				Load lock BP	2.8×10^{-6}
Target Material #1	Pt	Time:	~~60sec~~					Chamber BP	4.1×10^{-7}
Deposition Power #1:	45w	Time:	~~60sec~~	Film Thickness (nm):		Presput Power Film #1:		Time:	60sec
Target Material #2		Time:				Deposition rate (Å/s)			
Deposition Power #2:		Time:		Film Thickness (nm):		Presput Power Film #2:		Time:	
Number of Sample Holders With Substrates:				Comments		Deposition rate (Å/s)			
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Field	Value	Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	[illegible] Xie			Date:	12/10/10	Start Time	12:30	End Time	3:00
Process Gas (es)	Ar	Substrate:	quartz	Deposition Pressure (mT)				Load lock BP	[illegible]
Target Material #1	Ti	Time:	10 min	Pressure 10 mT/0.3				Chamber BP	4×10
Deposition Power #1:	90W	Time:		Film Thickness (nm):		Presput Power Film #1:		Time:	2 min
Target Material #2	Pt / Sc	Time:		10/3 [illegible] min		Deposition rate (Å/s)			
Deposition Power #2:	90/90 W	Time:	pressure	11/10	Film Thickness (nm):	Presput Power Film #2:		Time:	2/2 min
Number of Sample Holders With Substrates:				Comments		Deposition rate (Å/s)			
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date: TRIDIB GHOSH				Date:	11/22/2010	Start Time	1:30pm	End Time	3:00pm	Load lock BP	1×10⁻⁷
Process Gas (es)	Ar	Substrate:	Glass		Deposition Pressure (mT)		10mT	End Time		Chamber BP	5×10⁻⁷
Target Material #1	Ti/W	Time:	16s								
Deposition Power #1:	50W	Time:				Presput Power Film #1:	50W			Time:	2 min
					Film Thickness (nm):	2-3nm		Deposition rate (Å/s)			6-8 nm/min
Target Material #2	Au	Time:	2min								
Deposition Power #2:	50W	Time:				Presput Power Film #2:				Time:	2 min
					Film Thickness (nm):	40nm		Deposition rate (Å/s)			20 nm/min
Number of Sample Holders With Substrates:	2				Comments	Stepper Motor is not working well / shutters are not rotating well					
Total Sputter Time (all sample holders combined) Target #1					Total Sputter Time (all sample holders) Target #2						

Name/Date: 12/03/2010 Xiao Zhang				Date:	12/03/2010	Start Time	9:20	End Time		Load lock BP	4.6×10⁻⁷
Process Gas (es)	Ar	Substrate:	Si		Deposition Pressure (mT)		10mTorr			Chamber BP	3×10⁻⁶
Target Material #1	Ti	Time:	10 min								
Deposition Power #1:	90W	Time:	10 min			Presput Power Film #1:	7?			Time:	2
					Film Thickness (nm):			Deposition rate (Å/s)			
Target Material #2	Pt/Au	Time:	10/6								
Deposition Power #2:	90W	Time:	pre 11/10			Presput Power Film #2:	90W			Time:	2
					Film Thickness (nm):			Deposition rate (Å/s)			
Number of Sample Holders With Substrates:					Comments						
Total Sputter Time (all sample holders combined) Target #1					Total Sputter Time (all sample holders) Target #2						

Name/Date: ROHIT SHARMA				Date:	12/03/10	Start Time	12:30	End Time		Load lock BP	2.5×10⁻⁶
Process Gas (es)	Ar(RD)	Substrate:	Si		Deposition Pressure (mT)					Chamber BP	
Target Material #1	Ti/Pt	Time:	10/12 mins								
Deposition Power #1:	90/90W	~~Time~~: Pressure	10/11mT			Presput Power Film #1:				Time:	2/2 mins
					Film Thickness (nm):			Deposition rate (Å/s)			
Target Material #2	TiW/Pt	Time:	52/31 mins								
Deposition Power #2:	45W/90W	~~Time~~: Pressure	5/11mT			Presput Power Film #2:				Time:	2/1 min
					Film Thickness (nm):			Deposition rate (Å/s)			
Number of Sample Holders With Substrates:					Comments						
Total Sputter Time (all sample holders combined) Target #1					Total Sputter Time (all sample holders) Target #2						

Name/Date: Xiaoming Xie				Date:	12/06/2010	Start Time	11:00	End Time	12:30	Load lock BP	6×10⁻⁷
Process Gas (es)	Ar	Substrate:	Si		Deposition Pressure (mT)					Chamber BP	8×10⁻⁷
Target Material #1	Ti/W	Time:	10 min								
Deposition Power #1:	90W	Time:	pressure 10mT			Presput Power Film #1:	90W			Time:	2
					Film Thickness (nm):			Deposition rate (Å/s)			
Target Material #2	Pt/Au	Time:	10/8								
Deposition Power #2:	90/90	Time:	press 11/10			Presput Power Film #2:	90W			Time:	2/2
					Film Thickness (nm):			Deposition rate (Å/s)			
Number of Sample Holders With Substrates:					Comments						
Total Sputter Time (all sample holders combined) Target #1					Total Sputter Time (all sample holders) Target #2						

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date: SRI | **Date:** 11/16 | **Start Time:** 12:45 | **End Time:** 1:15 | **Load lock BP:** —

- Process Gas (es): Ar | Substrate: SiO2 | Deposition Pressure (mT): 5mt | End Time: | Chamber BP: 5x10-7
- Target Material #1: Au | Time:
- Deposition Power #1: 45W | Time: 10 sec | Presput Power Film #1: | Time:
- Film Thickness (nm): ~5nm | Deposition rate (Å/s):
- Target Material #2: | Time:
- Deposition Power #2: | Time: | Presput Power Film #2: | Time:
- Film Thickness (nm): | Deposition rate (Å/s):
- Number of Sample Holders With Substrates: | Comments
- Total Sputter Time (all sample holders combined) Target #1: 10 seconds | Total Sputter Time (all sample holders) Target #2:

Name/Date: Layne Williams | **Date:** 11/18 | **Start Time:** 2:00 | **End Time:** 6:45 | **Load lock BP:** —

- Process Gas (es): Ar/O2 | Substrate: Si/Glass | Deposition Pressure (mT): 10 | Chamber BP: 3.5x-7
- Target Material #1: Ti | ~~Time:~~ Gas: Ar/150 sccm
- Deposition Power #1: 90 | Time: 10 | Presput Power Film #1: 90 | Time: ~~10~~ 2
- Film Thickness (nm): | Deposition rate (Å/s):
- Target Material #2: InOx | ~~Time:~~ Gas: Ar/100, O2/100
- Deposition Power #2: 100 | Time: 35 | Presput Power Film #2: 100 | Time: ~~10~~, 10 post sputter
- Film Thickness (nm): | Deposition rate (Å/s):
- Number of Sample Holders With Substrates: 2 | Comments: Not pumping down chamber very well - Leak??
- Total Sputter Time (all sample holders combined) Target #1: 20 | Total Sputter Time (all sample holders) Target #2: 70

Name/Date: Layne Williams | **Date:** 11/19 | **Start Time:** 1:00 | **End Time:** 6:30 | **Load lock BP:** —

- Process Gas (es): Ar/O2 | Substrate: Si/Glass | Deposition Pressure (mT): 10 | Chamber BP: 3.5x-7
- Target Material #1: Ti | ~~Time:~~ Gas: Ar/150 sccm
- Deposition Power #1: 90 | Time: 10 | Presput Power Film #1: 90 | Time: 2
- Film Thickness (nm): | Deposition rate (Å/s):
- Target Material #2: | ~~Time:~~ Gas: Ar/100, O2/100 sccm
- Deposition Power #2: 100 | Time: 40 | Presput Power Film #2: 100 | Time: 10 pre, 10 post
- Film Thickness (nm): | Deposition rate (Å/s):
- Number of Sample Holders With Substrates: ~~2~~ 1 | Comments: Taking a very long time to pump down
- Total Sputter Time (all sample holders combined) Target #1: 10 | Total Sputter Time (all sample holders) Target #2: 40

Name/Date: MARUM | **Date:** 12/1/10 | **Start Time:** 10:30 | **End Time:** | **Load lock BP:** 2.1x10-6

- Process Gas (es): [illegible] | Substrate: | Deposition Pressure (mT): | Chamber BP: [illegible].7x10-7
- Target Material #1: [illegible] | Time: Gas [illegible] SCCM
- Deposition Power #1: [illegible] | Time: | Presput Power Film #1: | Time: 2:30 [illegible]
- Film Thickness (nm): 25nm | Deposition rate (Å/s): [illegible]
- Target Material #2: | Time:
- Deposition Power #2: | Time: | Presput Power Film #2: | Time:
- Film Thickness (nm): | Deposition rate (Å/s):
- Number of Sample Holders With Substrates: | Comments
- Total Sputter Time (all sample holders combined) Target #1: | Total Sputter Time (all sample holders) Target #2:

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date:	[illegible]/2010 Xiaoming [illegible]		Date:	11/03/2010	Start Time	11:30	End Time	Load lock BP	3.5x10-6
Process Gas (es)	Ar	Substrate:	Si	Deposition Pressure (mT)		10mT	End Time	Chamber BP	9.3x10-5
Target Material #1	Ti	Time:	10 min		Presput Power Film #1:	90		Time:	2
Deposition Power #1:	90	Time:	Pressure 10 Torr	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Pt (Au)	Time:	(10 c/)		Presput Power Film #2:	90		Time:	2 (2)
Deposition Power #2:	90W	Time:	Pressure ([illegible])	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date:	Layne Williams		Date:	11/12/10	Start Time	12:45	End Time 5:30	Load lock BP	1.7x-6
Process Gas (es)		Substrate:	Si/Glass	Deposition Pressure (mT)				Chamber BP	3.2x-7
Target Material #1	Ti	~~Time:~~ Gas	Ar/150 sccm		Presput Power Film #1:	90		Time:	2
Deposition Power #1:	90	Time:	10	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	IrOx	~~Time:~~ Gas	Ar/100, O2/100 sccm		Presput Power Film #2:	100		Time:	20, 10 post
Deposition Power #2:	100	Time:	35	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	2			Comments					
Total Sputter Time (all sample holders combined) Target #1	20			Total Sputter Time (all sample holders) Target #2	70				

Name/Date:	Raja Kumar Manthena		Date:	11/15/10	Start Time	1:00 pm	End Time 2:00 pm	Load lock BP	Not Known
Process Gas (es)	Ar	Substrate:	Si with ARC	Deposition Pressure (mT)	10			Chamber BP	5.4x10-7
Target Material #1	Pt	Time:			Presput Power Film #1:	45		Time:	180sec
Deposition Power #1:	45w	Time:	30sec	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:			Presput Power Film #2:			Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date:	Raja Kumar Manthena		Date:	11/16/10	Start Time	9:00 AM	End Time 10:00 AM	Load lock BP	Not Known
Process Gas (es)	Ar	Substrate:	Si with ARC	Deposition Pressure (mT)	10			Chamber BP	5.6x10-7
Target Material #1	Pt	Time:			Presput Power Film #1:	45w		Time:	120sec
Deposition Power #1:	45w	Time:	30sec	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Pt	Time:			Presput Power Film #2:	42		Time:	180sec
Deposition Power #2:	42w	Time:	30sec	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1	30sec			Total Sputter Time (all sample holders) Target #2	30sec				

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date: Rohit Sharma		Date: 10/21/10	Start Time 3:00	End Time 5:00	Load lock BP 3.7x10^-6
Process Gas (es): Ar(150)	Substrate: Si	Deposition Pressure (mT) ←		End Time	Chamber BP 4x10^-7
Target Material #1: Ti	Time: 10mins		Presput Power Film #1:		Time: 2mins
Deposition Power #1: 90W	~~Time:~~ Pr. 10mT	Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2: Pt/Au	Time: 10/6mins		Presput Power Film #2:		Time: 2/1mins
Deposition Power #2: 80/90	~~Time:~~ Pr. 11/10mT	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments			
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2			

Name/Date: Rohit Sharma		Date: 10/22/10	Start Time 8:40	End Time 10:30	Load lock BP 3.7x10^-6
Process Gas (es): Ar(110)	Substrate: Si	Deposition Pressure (mT)		←	Chamber BP 3.2x10^-7
Target Material #1: TiW	Time: 25mins		Presput Power Film #1:		Time: 2 mins
Deposition Power #1: 45W	~~Time:~~ Pr. 5mT	Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2:	Time:		Presput Power Film #2:		Time:
Deposition Power #2:	Time:	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments			
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2			

Name/Date: Layne Williams		Date: 10/22/10	Start Time 1:00	End Time	Load lock BP 1.4x^-6
Process Gas (es): Ar	Substrate: Si	Deposition Pressure (mT) 5/11			Chamber BP 2.1x^-7
Target Material #1: Ti	~~Time:~~ Gas	Ar/150 sccm	Presput Power Film #1: 90		Time: 2
Deposition Power #1: ~~75~~ 90	Time: 10	Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2: Pt	~~Time:~~ Gas	Ar/150 sccm	Presput Power Film #2: 90		Time: 2
Deposition Power #2: 90	Time: 14min	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates: 2		Comments			
Total Sputter Time (all sample holders combined) Target #1: 20		Total Sputter Time (all sample holders) Target #2: 28			

Name/Date: Sandeep (BR)		Date: 10/29/10	Start Time 1pm	End Time 3pm	Load lock BP 2x10^-6
Process Gas (es): Ar/O2	Substrate: Si	Deposition Pressure (mT) 10			Chamber BP 4x10^-7
Target Material #1: Ti	Time: 5min		Presput Power Film #1: 90		Time: 2min
Deposition Power #1: 90	Time: —	Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2: Ir	Time: —		Presput Power Film #2: 100		Time: 2min
Deposition Power #2: 100W	Time: 20min	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates: ONE		Comments			
Total Sputter Time (all sample holders combined) Target #1: 5		Total Sputter Time (all sample holders) Target #2: 20			

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date: Y'anzong Xie		Date: 11/03/10	Start Time: 10:30	End Time: 12:40	Load lock BP: 4.5×10^{-7}
Process Gas (es): Ar	Substrate: Si	Deposition Pressure (mT):		End Time:	Chamber BP: 1.2×10^{-6}
Target Material #1: Ti	Time: 10 min				
Deposition Power #1: 90 W	Time: Pressure 10 mT	Film Thickness (nm):	Presput Power Film #1: 90 W	Deposition rate (Å/s):	Time: 10 min
Target Material #2: Pt (Au)	Time: 10 (6) min				
Deposition Power #2: 90 W	Time: pressure 11 mT	Film Thickness (nm):	Presput Power Film #2: ~~[illegible]~~ 90 W	Deposition rate (Å/s):	Time: 5 min
Number of Sample Holders With Substrates:		Comments			
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2			

Name/Date: Layne Williams		Date: 11/3/10	Start Time: 1:00	End Time: 4:00	Load lock BP: 1.0x-6
~~Process Gas (es)~~	Substrate: Si	Deposition Pressure (mT): 10			Chamber BP: 2.9x-7
Target Material #1: Ti	~~Time:~~ Gas: Ar/150 sccm				
Deposition Power #1: 90	Time: 10 min	Film Thickness (nm):	Presput Power Film #1: 90	Deposition rate (Å/s):	Time: 2
Target Material #2: Ir	~~Time:~~ Gas: Ar/100 O_2/100 sccm				
Deposition Power #2: 100	Time: 40 min	Film Thickness (nm):	Presput Power Film #2: 100	Deposition rate (Å/s):	Time: 10
Number of Sample Holders With Substrates: 1		Comments			
Total Sputter Time (all sample holders combined) Target #1	10	Total Sputter Time (all sample holders) Target #2	35		

Name/Date: Bennion Redd		Date: 11/04/10	Start Time: 10:45	End Time: 2:00	Load lock BP: ?
Process Gas (es): Ar, O_2	Substrate: Ti PR	Deposition Pressure (mT): 10			Chamber BP: 6x-7
Target Material #1: IrOx	Time: 50 min				
Deposition Power #1: 50 W	Time:	Film Thickness (nm):	Presput Power Film #1:	Deposition rate (Å/s):	Time:
Target Material #2:	Time:				
Deposition Power #2:	Time:	Film Thickness (nm):	Presput Power Film #2:	Deposition rate (Å/s):	Time:
Number of Sample Holders With Substrates:		Comments			
Total Sputter Time (all sample holders combined) Target #1	72 min	Total Sputter Time (all sample holders) Target #2			

Name/Date: Mohit		Date: 11/05	Start Time: 1500	End Time: 1700	Load lock BP: 1×10^{-6}
Process Gas (es): Ar	Substrate: Si	Deposition Pressure (mT): 10 mT			Chamber BP: 3×10^{-7}
Target Material #1: Pt	Time: 6 min				
Deposition Power #1: 90 W	Time:	Film Thickness (nm):	Presput Power Film #1:	Deposition rate (Å/s):	Time: 20 min
Target Material #2: –	Time:				
Deposition Power #2: –	Time:	Film Thickness (nm):	Presput Power Film #2:	Deposition rate (Å/s):	Time:
Number of Sample Holders With Substrates:		Comments			
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2			

Comments:

TM Vacuum Sputter Deposition LOG

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	[illegible]anzong Xie	Date:	Oct 17	Start Time	11:00	End Time	12:40
Load lock BP	3×10⁻⁶	Process Gas (es)	Ar	Substrate:	quartz	Deposition Pressure (mT)	10
End Time		Chamber BP	4.6×10⁻⁷	Target Material #1	Ti	Time:	
Deposition Power #1:	45	Time:	10 min	Film Thickness (nm):		Presput Power Film #1:	45
Time:	2 mins	Deposition rate (Å/s)		Target Material #2	Pt (Au)	Time:	Pressure 10 (17) mT (11(20) mT)
Deposition Power #2:	45(45)	Time:	10 (6) min	Film Thickness (nm):		Presput Power Film #2:	45(45)
Time:	2 mins (2 mins)	Deposition rate (Å/s)		Number of Sample Holders With Substrates:		Comments	
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	ROHIT SHARMA	Date:	10/18/10	Start Time	1:30	End Time	3:00
Load lock BP	3.6×10⁻⁶	Process Gas (es)	Ar (110)	Substrate:	Si	Deposition Pressure (mT)	110
Chamber BP	4×10⁻⁷	Target Material #1	Ti	Time:	10 mins	Deposition Power #1:	90W
Time:	Pr. 10 mT	Film Thickness (nm):		Presput Power Film #1:		Time:	2 mins
Deposition rate (Å/s)		Target Material #2	Pt / Au	Time:	10 / 6 mins	Deposition Power #2:	90/90W
Time:	Pr. 10/20 mT	Film Thickness (nm):		Presput Power Film #2:		Time:	2/2 mins
Deposition rate (Å/s)		Number of Sample Holders With Substrates:		Comments		Total Sputter Time (all sample holders combined) Target #1	
Total Sputter Time (all sample holders) Target #2							

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	ROHIT SHARMA	Date:	10/19/10	Start Time	3:15	End Time	4:30
Load lock BP	3.5×10⁻⁶	Process Gas (es)	Ar (110)	Substrate:	Si	Deposition Pressure (mT)	110
Chamber BP	7.6×10⁻⁷	Target Material #1	TiW	Time:	47 mins	Deposition Power #1:	45W
Time:	Pr. 5 mT	Film Thickness (nm):	[illegible]	Presput Power Film #1:	[illegible]	Time:	2 mins
Deposition rate (Å/s)		Target Material #2		Time:		Deposition Power #2:	
Time:		Film Thickness (nm):	[illegible]	Presput Power Film #2:	[illegible]	Time:	
Deposition rate (Å/s)		Number of Sample Holders With Substrates:		Comments		Total Sputter Time (all sample holders combined) Target #1	
Total Sputter Time (all sample holders) Target #2							

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	[illegible] GHOSH	Date:	10/20/10	Start Time	5:30	End Time	7:30
Load lock BP	2.2×10⁻⁷	Process Gas (es)	Ar	Substrate:	Glass	Deposition Pressure (mT)	10 mT
Chamber BP	2.5×10⁻⁷	Target Material #1	Ti/W	Time:		Deposition Power #1:	50W
Time:	16 s	Film Thickness (nm):	2-3nm	Presput Power Film #1:	50W	Time:	2 min
Deposition rate (Å/s)	6-8 nm/min	Target Material #2	Au	Time:		Deposition Power #2:	50W
Time:	2 min	Film Thickness (nm):	40 nm	Presput Power Film #2:	50W	Time:	2 min
Deposition rate (Å/s)	20 nm/min	Number of Sample Holders With Substrates:	2	Comments		Total Sputter Time (all sample holders combined) Target #1	
Total Sputter Time (all sample holders) Target #2							

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date: [illegible] Park		Date:	10/13/2010	Start Time	10:00	End Time	11:00	Load lock BP	8.0×10^{-7}
Process Gas (es)	Ar	Substrate:	Teflon	Deposition Pressure (mT)	10	End Time		Chamber BP	2×10^{-7}
Target Material #1	Cr	Time:	1						
				Presput Power Film #1:				Time:	0.5
Deposition Power #1:	90	Time:		Film Thickness (nm):	8	Deposition rate (Å/s)	80		
Target Material #2	Au	Time:							
				Presput Power Film #2:				Time:	0.5
Deposition Power #2:	50	Time:	2.5	Film Thickness (nm):	50	Deposition rate (Å/s)	200		
Number of Sample Holders With Substrates:	1			Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date: Layne Williams		Date:	10/13/10	Start Time	2:00	End Time	5:00	Load lock BP	1.5×10^{-6}
Process Gas (es)		Substrate:		Deposition Pressure (mT)				Chamber BP	3×10^{-7}
Target Material #1	Ti	~~Time:~~ Gas	Ar/150 sccm	Presput Power Film #1:	90			Time:	2
Deposition Power #1:	90	Time:	10 min	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	IrOx	~~Time:~~ Gas	Ar/100, O_2/100 sccm	Presput Power Film #2:	100			Time:	10
Deposition Power #2:	100	Time:	35 min	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	2			Comments	Both chucks rotating well, 10 min post-sputter				
Total Sputter Time (all sample holders combined) Target #1	20			Total Sputter Time (all sample holders) Target #2	70				

Name/Date: Bennion Redd		Date:	10/15/10	Start Time	1:45	End Time		Load lock BP	8.8×10^{-7}
Process Gas (es)	Ar	Substrate: PR/Pt		Deposition Pressure (mT)	10			Chamber BP	2.8×10^{-7}
Target Material #1	Ti	Time: 2 min	Ar 150 sccm	Presput Power Film #1:				Time:	
Deposition Power #1:	45 W	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:		Presput Power Film #2:				Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1	6 min			Total Sputter Time (all sample holders) Target #2					

Name/Date: Layne Williams		Date:	10/19/10	Start Time	2:00	End Time	5:30	Load lock BP	2×10^{-6}
Process Gas (es)		Substrate:	Si/Glass	Deposition Pressure (mT)				Chamber BP	7×10^{-7}
Target Material #1	Ti	~~Time:~~ Gas	Ar/150 sccm	Presput Power Film #1:	90			Time:	2
Deposition Power #1:	90	Time:	10	Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	IrOx	~~Time:~~ Gas	Ar/100, O_2/100 sccm	Presput Power Film #2:	100			Time:	12
Deposition Power #2:	100	Time:	35	Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	2			Comments	10 min post-sputter w/ Ir target				
Total Sputter Time (all sample holders combined) Target #1	20			Total Sputter Time (all sample holders) Target #2	70				

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date:	ROHIT SHARMA	Date:	10/05	Start Time	4:00	End Time	530
Load lock BP	4.1x10-8	Chamber BP	3.6x10-7				
Process Gas (es)	Ar(100)	Substrate:	Si	Deposition Pressure (mT)	30mW	End Time	—
Target Material #1	TiW	Time:		Presput Power Film #1:		Time:	2mins
Deposition Power #1:	45W	~~Time:~~ Presure	5mT	Film Thickness (nm):	—	Deposition rate (Å/s)	—
Target Material #2		Time:		Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments					
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Name/Date:	Sandeep (BR)	Date:	10/6/10	Start Time	1pm	End Time	3pm
Load lock BP	2x10-6	Chamber BP	2x10-7				
Process Gas (es)	Ar 10	Substrate:	Si	Deposition Pressure (mT)	10 mTorr		
Target Material #1	Ti	Time:	5min	Presput Power Film #1:	1min	Time:	90W
Deposition Power #1:	90W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	Ir	Time:	20 min	Presput Power Film #2:	1min	Time:	100W
Deposition Power #2:	100W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:	One	Comments					
Total Sputter Time (all sample holders combined) Target #1	5	Total Sputter Time (all sample holders) Target #2	20 min				

Name/Date:	Jungwoo Park	Date:	10/8/10	Start Time	9:00pm	End Time	11:00pm
Load lock BP	1.5x10-6	Chamber BP	4.1x10-7				
Process Gas (es)	Ar	Substrate:	Teflon	Deposition Pressure (mT)	10mT		
Target Material #1	Cr	Time:	1	Presput Power Film #1:		Time:	0.5
Deposition Power #1:	90W	Time:		Film Thickness (nm):	8nm	Deposition rate (Å/s)	8nm/min
Target Material #2	Au	Time:	2.5	Presput Power Film #2:		Time:	0.5
Deposition Power #2:	50W	Time:		Film Thickness (nm):	50nm	Deposition rate (Å/s)	20nm/min
Number of Sample Holders With Substrates:	1	Comments					
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Name/Date:	Sandeep (BR)	Date:	10/12/10	Start Time	3pm	End Time	5:20pm
Load lock BP	2x10-6	Chamber BP	2x10-7				
Process Gas (es)	Ar(10)	Substrate:	Si	Deposition Pressure (mT)	10 mTorr		
Target Material #1	Ti	Time:	5min	Presput Power Film #1:	90W	Time:	1min
Deposition Power #1:	90W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	Sr	Time:	20 min	Presput Power Film #2:	100W	Time:	2min
Deposition Power #2:	100W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:	One	Comments					
Total Sputter Time (all sample holders combined) Target #1	5	Total Sputter Time (all sample holders) Target #2	20				

Comments: One Holder NOT rotating

TM Vacuum Sputter Deposition LOG

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Layne	Date:	9/30/10	Start Time		End Time	
Load lock BP		Process Gas (es)		Substrate:		Deposition Pressure (mT)	
End Time		Chamber BP		Target Material #1	DID NOT USE - SYSTEM NOT	Time:	
Presput Power Film #1:		Time:		Deposition Power #1:	AT PROPER VACUUM	Time:	
Film Thickness (nm):		Deposition rate (Å/s)		Target Material #2		Time:	
Presput Power Film #2:		Time:		Deposition Power #2:		Time:	
Film Thickness (nm):		Deposition rate (Å/s)		Number of Sample Holders With Substrates:		Comments	Did Not Use - System had not reached proper vacuum after maintenance
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Layne	Date:	10/4/10	Start Time	1:00	End Time	5:00
Load lock BP	1.3x-6	Process Gas (es)		Substrate:	Glass/Si	Deposition Pressure (mT)	10
Chamber BP	1.8x-7	Target Material #1	Ti	~~Time:~~ Gas	Ar/150 sccm	Presput Power Film #1:	90
Time:	2	Deposition Power #1:	90	Time:	10	Film Thickness (nm):	100
Deposition rate (Å/s)	10	Target Material #2	InOx	~~Time:~~ Gas	Ar/100 sccm, O_2/10 sccm	Presput Power Film #2:	100
Time:	10 / 10 post sputter	Deposition Power #2:	100	Time:	30	Film Thickness (nm):	
Deposition rate (Å/s)		Number of Sample Holders With Substrates:	2	Comments	10 min pre and post sputter w/ Ar only		
Total Sputter Time (all sample holders combined) Target #1	20	Total Sputter Time (all sample holders) Target #2	60				

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Bennion Redd	Date:	10/5/10	Start Time	10:30	End Time	
Load lock BP		Process Gas (es)	Ar	Substrate:	Si/N/PR	Deposition Pressure (mT)	10
Chamber BP	3.1x-7	Target Material #1	Ti	Time:	2 min.	Presput Power Film #1:	
Time:		Deposition Power #1:	45 W	Time:		Film Thickness (nm):	
Deposition rate (Å/s)		Target Material #2	Pt	Time:	25 min	Presput Power Film #2:	
Time:		Deposition Power #2:	50 W	Time:		Film Thickness (nm):	
Deposition rate (Å/s)		Number of Sample Holders With Substrates:		Comments			
Total Sputter Time (all sample holders combined) Target #1	5	Total Sputter Time (all sample holders) Target #2	52				

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Rohit Sharma	Date:	10/7/10	Start Time	1:00	End Time	2:30
Load lock BP	4x10^-6	Process Gas (es)	Ar(150)	Substrate:	Si	Deposition Pressure (mT)	— —
Chamber BP	4x10^-7	Target Material #1	Ti	Time:	10 mins	Presput Power Film #1:	
Time:	2 mins	Deposition Power #1:	90 W	~~Time:~~ Pressure	10 mT	Film Thickness (nm):	—
Deposition rate (Å/s)	—	Target Material #2	Pt/Au	Time:	10/6 mins	Presput Power Film #2:	
Time:	2/2 mins	Deposition Power #2:	90/90	~~Time:~~ Pressure	11/20 mT	Film Thickness (nm):	
Deposition rate (Å/s)		Number of Sample Holders With Substrates:		Comments			
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Comments:

TM Vacuum Sputter Deposition LOG

Entry 1

- Name/Date: Abhijit Mondal / 9/27/2010
- Date: 9/27/2010 — Start Time: 9:30am — End Time: 11:00 a.m. — Load lock BP:
- Process Gas (es): Ar, Ar/O_2, Ar — Substrate: Polycarbonate
- Deposition Pressure (mT): — End Time: — Chamber BP: 3.2×10^{-7} T
- Target Material #1: Ti — Time: 03:00
- Presput Power Film #1: — Time: 00:2:00
- Deposition Power #1: 45 W — Time:
- Film Thickness (nm): — Deposition rate (Å/s):
- Target Material #2: Au — Time: 00:5:00
- Presput Power Film #2: — Time: 00:2:00
- Deposition Power #2: 50 W — Time:
- Film Thickness (nm): — Deposition rate (Å/s):
- Number of Sample Holders With Substrates: 1
- Comments:
- Total Sputter Time (all sample holders combined) Target #1: 8:00
- Total Sputter Time (all sample holders) Target #2:

Entry 2

- Name/Date: Layne
- Date: 9/28/10 — Start Time: 1:30 — End Time: 6:00 — Load lock BP: 1.2×10^{-6}
- Process Gas (es): — Substrate: Glass/Si
- Deposition Pressure (mT): 10 — Chamber BP: 2×10^{-7}
- Target Material #1: Ti — ~~Time:~~ Gas: Ar/150 sccm
- Presput Power Film #1: 70 — Time: 2 min
- Deposition Power #1: 90W — Time: 10 min
- Film Thickness (nm): 332 — Deposition rate (Å/s): 130 – plasma ~~had~~ flickered during deposition
- Target Material #2: IrOx — ~~Time:~~ Gas: Ar/100, O_2/100 sccm
- Presput Power Film #2: 100 — Time: 12 min
- Deposition Power #2: 100 — Time: ~~20 min~~ 25 min
- Film Thickness (nm): — Deposition rate (Å/s):
- Number of Sample Holders With Substrates: 2
- Comments: Chuck 2 would not rotate – asked for help
- Total Sputter Time (all sample holders combined) Target #1: 20 min
- Total Sputter Time (all sample holders) Target #2: 50 min

Entry 3

- Name/Date: Layne
- Date: 9/29/10 — Start Time: 10:30 — End Time: 11:30 — Load lock BP: —
- Process Gas (es): — Substrate:
- Deposition Pressure (mT): 10 — Chamber BP: 2.5×10^{-7}
- Target Material #1: Ir — ~~Time:~~ Gas: Ar/100, O_2/100
- Presput Power Film #1: 100 — Time: 10
- Deposition Power #1: 100 — Time: ~~35~~ 35
- Film Thickness (nm): 700 — Deposition rate (Å/s): 20 – no plasma flicker
- Target Material #2: — Time:
- Presput Power Film #2: — Time:
- Deposition Power #2: — Time:
- Film Thickness (nm): — Deposition rate (Å/s):
- Number of Sample Holders With Substrates: 1
- Comments: 10 min post sputter
- Total Sputter Time (all sample holders combined) Target #1: 55
- Total Sputter Time (all sample holders) Target #2:

Continue from yesterday

Entry 4

- Name/Date: Kevin
- Date: 9/29/10 — Start Time: 12:00 — End Time: 1:45 — Load lock BP: 2.1×10^{-6}
- Process Gas (es): — Substrate:
- Deposition Pressure (mT): — Chamber BP: 2.9×10^{-7}
- Target Material #1: — Time:
- Presput Power Film #1: — Time:
- Deposition Power #1: — Time:
- Film Thickness (nm): — Deposition rate (Å/s):
- Target Material #2: — Time:
- Presput Power Film #2: — Time:
- Deposition Power #2: — Time:
- Film Thickness (nm): — Deposition rate (Å/s):
- Number of Sample Holders With Substrates:
- Comments: Troubleshoot system/Maintenance
- Total Sputter Time (all sample holders combined) Target #1:
- Total Sputter Time (all sample holders) Target #2:

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date: Xianzong Xie		Date: 09/17	Start Time 10:00am	End Time 1pm	Load lock BP	3×10⁻⁶
Process Gas (es)	Ar	Substrate: Si	Deposition Pressure (mT)	End Time	Chamber BP	3×10⁻⁶ torr 4.5×10⁻⁷
Target Material #1	Ti	Time: 10 min	Presput Power Film #1: 90		Time:	2 min
Deposition Power #1:	90 W	Time: pressure 10 mTorr	Film Thickness (nm):	Deposition rate (Å/s)		
Target Material #2	Pt/Au	Time: 10/6 min	Presput Power Film #2: 40		Time:	2/2 min
Deposition Power #2:	90/40 W	Time: pre 11/20 mTorr	Film Thickness (nm):	Deposition rate (Å/s)		
Number of Sample Holders With Substrates:			Comments			
Total Sputter Time (all sample holders combined) Target #1			Total Sputter Time (all sample holders) Target #2			

Name/Date: Xianzong Xie		Date: 09/17	Start Time 11:30am	End Time 1:40pm	Load lock BP	2×10⁻⁷
Process Gas (es)	Argon	Substrate: Si	Deposition Pressure (mT)		Chamber BP	7.2×10⁻⁷
Target Material #1	Ti	Time: pressure 10 mTorr	Presput Power Film #1: 90W		Time:	2 min
Deposition Power #1:	90 W	Time: 10 mins	Film Thickness (nm):	Deposition rate (Å/s)		
Target Material #2	Pt/Au	Time: 10 10/6 min	Presput Power Film #2: 80		Time:	2 min
Deposition Power #2:	90/90	Time: pressure 11/20 mTorr	Film Thickness (nm):	Deposition rate (Å/s)		
Number of Sample Holders With Substrates:			Comments			
Total Sputter Time (all sample holders combined) Target #1			Total Sputter Time (all sample holders) Target #2			

Name/Date: ROHIT SHARMA		Date: 09/21	Start Time 11:30	End Time 12:45	Load lock BP	3.5×10⁻⁶
Process Gas (es)	Ar (150)	Substrate: Si	Deposition Pressure (mT) —	—	Chamber BP	4×10⁻⁷
Target Material #1	Ti	Time: 10 mins	Presput Power Film #1:		Time:	2 mins
Deposition Power #1:	90 W	Time: Pressure 10 mT	Film Thickness (nm):	Deposition rate (Å/s)		
Target Material #2	Pt/Au	Time: 10/6 mins	Presput Power Film #2:		Time:	2/2 mins
Deposition Power #2:	90/90 W	Time: Pressure 11/20 mT	Film Thickness (nm):	Deposition rate (Å/s)		
Number of Sample Holders With Substrates:			Comments			
Total Sputter Time (all sample holders combined) Target #1			Total Sputter Time (all sample holders) Target #2			

Name/Date: ROHIT SHARMA		Date: 09/21	Start Time 1:30	End Time 3:00	Load lock BP	3.5×10⁻⁶
Process Gas (es)	Ar (150)	Substrate: Si	Deposition Pressure (mT)	5 mT	Chamber BP	3.5×10⁻⁷
Target Material #1	TiW	Time: 30 mins	Presput Power Film #1:		Time:	2 mins.
Deposition Power #1:	45 W	Time: 30 mins	Film Thickness (nm):	Deposition rate (Å/s)		
Target Material #2		Time:	Presput Power Film #2:		Time:	
Deposition Power #2:		Time:	Film Thickness (nm):	Deposition rate (Å/s)		
Number of Sample Holders With Substrates:			Comments			
Total Sputter Time (all sample holders combined) Target #1			Total Sputter Time (all sample holders) Target #2			

Comments:

TM Vacuum Sputter Deposition LOG

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Raj (BR)	Date:	09/07/10	Start Time	2:00pm	End Time	
Load lock BP	1X10-5	Process Gas (es)	Ar	Substrate:	Si	Deposition Pressure (mT)	20
End Time		Chamber BP	8.5X10-7	Target Material #1	Ti	Time:	5
Presput Power Film #1:	90	Time:	2 Min	Deposition Power #1:	90	Time:	
Film Thickness (nm):		Deposition rate (Å/s)		Target Material #2	Pt	Time:	12
Presput Power Film #2:	90	Time:	2 Min -	Deposition Power #2:	90	Time:	
Film Thickness (nm):		Deposition rate (Å/s)		Number of Sample Holders With Substrates:	ONE	Comments	
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	ROHIT SHARMA	Date:	09/15/10	Start Time	3.80	End Time	5.30
Load lock BP	3.1x10-6	Process Gas (es)	Ar (110)	Substrate:	Si	Deposition Pressure (mT)	—
Chamber BP	5x10-7	Target Material #1	Ti	Time:	10mins	Presput Power Film #1:	
Time:	2min	Deposition Power #1:	90 W	~~Time~~: Pressure	10mT	Film Thickness (nm):	
Deposition rate (Å/s)		Target Material #2	Pt / Au	Time:	10 / 6 mins	Presput Power Film #2:	
Time:	2/2 min	Deposition Power #2:	90 / 80W	~~Time~~ Press	11/20mT	Film Thickness (nm):	
Deposition rate (Å/s)		Number of Sample Holders With Substrates:		Comments	TMV was down whole morning/afternoon [Thats y started late]		
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	ROHIT SHARMA	Date:	09	Start Time	5:00	End Time	6:00
Load lock BP	3.2x10-6	Process Gas (es)	Ar (110)	Substrate:	Si	Deposition Pressure (mT)	
Chamber BP		Target Material #1	TiW	Time:	30mins	Presput Power Film #1:	
Time:	2 min	Deposition Power #1:	45 W	~~Time~~: Pres	5mT	Film Thickness (nm):	
Deposition rate (Å/s)		Target Material #2		Time:		Presput Power Film #2:	
Time:		Deposition Power #2:		Time:		Film Thickness (nm):	
Deposition rate (Å/s)		Number of Sample Holders With Substrates:		Comments			
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Sandeep (BR)	Date:	9/16/10	Start Time	12pm	End Time	2:30pm
Load lock BP	2x10-6	Process Gas (es)	Ar/02	Substrate:	Si	Deposition Pressure (mT)	10
Chamber BP	1x10-7	Target Material #1	Ti	Time:	5min	Presput Power Film #1:	90
Time:	2 min	Deposition Power #1:	90W	Time:		Film Thickness (nm):	
Deposition rate (Å/s)		Target Material #2	Ir	Time:	20min	Presput Power Film #2:	100W
Time:	5min	Deposition Power #2:	100W	Time:		Film Thickness (nm):	
Deposition rate (Å/s)		Number of Sample Holders With Substrates:	ONE	Comments			
Total Sputter Time (all sample holders combined) Target #1	5	Total Sputter Time (all sample holders) Target #2	20 min				

Comments: Problem in substrate rotation

TM Vacuum Sputter Deposition LOG

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Sandeep	Date:	9/7/10	Start Time	10:55a	End Time	12:15p
Process Gas (es)	Ar/O2	Substrate:	Si	Deposition Pressure (mT)	10	End Time	
Target Material #1	Ti	Time:	10 min	Presput Power Film #1:		Time:	2 min
Deposition Power #1:	90W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	Ir	Time:	40 min	Presput Power Film #2:	100W	Time:	5 min
Deposition Power #2:	100W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:	One	Comments	V = 370 I = .28				
Total Sputter Time (all sample holders combined) Target #1	10 min	Total Sputter Time (all sample holders) Target #2	40 min				

Load lock BP: 15 x 10^-6 Torr; Chamber BP: 1.7 x 10^-7 Torr

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Hannwelin Steinebach	Date:	9/7/10	Start Time	2:30 PM	End Time	3:45PM
Process Gas (es)	Ar	Substrate:	SiO2	Deposition Pressure (mT)	20/10		
Target Material #1	Ti	Time:	5 min	Presput Power Film #1:	90W	Time:	2 min
Deposition Power #1:	90W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	Pt	Time:	12 min	Presput Power Film #2:	90W	Time:	2 min
Deposition Power #2:	90W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:	one	Comments					
Total Sputter Time (all sample holders combined) Target #1	5 min	Total Sputter Time (all sample holders) Target #2	12 min				

Load lock BP: 2.9·10^-6 Torr; Chamber BP: 3.1·10^-7 Torr

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	ROHIT SHARMA	Date:	9/8/10	Start Time	11:00	End Time	1:00
Process Gas (es)	Ar(150)	Substrate:	Si	Deposition Pressure (mT)	—		
Target Material #1	Ti	Time:	10 mins	Presput Power Film #1:		Time:	2 mins
Deposition Power #1:	90W	~~Time:~~ Pressure	10mT	Film Thickness (nm):	—	Deposition rate (Å/s)	—
Target Material #2	Pt/Au	Time:	10/6 mins	Presput Power Film #2:		Time:	2/2 mins
Deposition Power #2:	90/90W	~~Time:~~ Pressure	11/20mT	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments					
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Load lock BP: 3 x 10^-2; Chamber BP: 4 x 10^-2

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	ROHIT SHARMA	Date:	9/8/10	Start Time	2:30	End Time	2:45
Process Gas (es)	Ar(150)	Substrate:		Deposition Pressure (mT)			
Target Material #1	TiW	Time:	30 mins	Presput Power Film #1:		Time:	2 mins
Deposition Power #1:	41W	~~Time:~~ Pressure	5mT	Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2		Time:		Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments					
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Load lock BP: 3 x 10^-6; Chamber BP: 4 x 10^-7

Comments:

TM Vacuum Sputter Deposition LOG

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Rohit Sharma	Date:	08/20/10	Start Time	2:45	End Time	3:30
Process Gas (es)	Ar(150)	Substrate:	Si	Deposition Pressure (mT)		End Time	—
Target Material #1	TiW	Time:	30 mins	Presput Power Film #1:		Time:	2 mins
Deposition Power #1:	45W	~~Time:~~ Pressure	5.1mT	Film Thickness (nm):	—	Deposition rate (Å/s)	—
Target Material #2		Time:		Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:				Comments		Load lock BP	—
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2		Chamber BP	4.2x10-7

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Rohit Sharma	Date:	08/31/10	Start Time	12:45	End Time	1:45
Process Gas (es)	Ar(150)	Substrate:	Si	Deposition Pressure (mT)	—	Load lock BP	—
Target Material #1	Ti	Time:	10 mins	Presput Power Film #1:		Chamber BP	4x10-7
Deposition Power #1:	90W	~~Time:~~ Pressure	10mT	Film Thickness (nm):	—	Deposition rate (Å/s)	—
Target Material #2	Pt/Au	Time:	10/6 mins	Presput Power Film #2:		Time (Film #1)	2 mins
Deposition Power #2:	90/90W	~~Time:~~ Pressure	11/20mT	Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:				Comments		Time (Film #2)	2/2 min
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2			

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Rohit Sharma	Date:	08/31/10	Start Time	2:45	End Time	3:45
Process Gas (es)	Ar(110)	Substrate:	Si	Deposition Pressure (mT)	—	Load lock BP	—
Target Material #1	TiW	Time:	30 mins	Presput Power Film #1:		Chamber BP	3x10-7
Deposition Power #1:	45W	~~Time:~~ Pr.	5mT	Film Thickness (nm):	—	Deposition rate (Å/s)	
Target Material #2		Time:		Presput Power Film #2:		Time (Film #1)	2 mins
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:				Comments		Time (Film #2)	
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2			

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Layne Williams	Date:	9/2/10	Start Time	3:00	End Time	5:00
Process Gas (es)		Substrate:	Si/Glass	Deposition Pressure (mT)	10	Load lock BP	1.7x10-6
Target Material #1	Ti	~~Time:~~ Gas:	Ar/150 sccm	Presput Power Film #1:	90	Chamber BP	2.7x-7
Deposition Power #1:	90	Time:	10 min	Film Thickness (nm):	100 nm	Deposition rate (Å/s)	
Target Material #2	IrOx	~~Time:~~ Gas	O2/100, Ar/100 sccm	Presput Power Film #2:	100	Time (Film #1)	2
Deposition Power #2:	100	Time:	42	Film Thickness (nm):	450	Deposition rate (Å/s)	
Number of Sample Holders With Substrates:	1			Comments	10 min post sputter - Ar only	Time (Film #2)	12
Total Sputter Time (all sample holders combined) Target #1	10			Total Sputter Time (all sample holders) Target #2	42		

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date:	ROHIT SHARMA	Date:	08/26/10	Start Time	10:30	End Time	12:30	Load lock BP	—
Process Gas (es)	Ar/150	Substrate:	Si	Deposition Pressure (mT)		End Time		Chamber BP	3.5x10-7
Target Material #1	TiW	Time:	30mins			Presput Power Film #1:		Time:	2mins
Deposition Power #1:	45W	~~Time~~: Pressure	5mT	Film Thickness (nm):	—	Deposition rate (Å/s)			—
Target Material #2		Time:				Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date:	Yan Xie	Date:	08/27/10	Start Time	3:30	End Time	4:30	Load lock BP	4.5x10-7
Process Gas (es)	Ar	Substrate:	SiN	Deposition Pressure (mT)	~~10~~		10mT	Chamber BP	↓
Target Material #1	Au	Time:	5 mins			Presput Power Film #1:		Time:	2 mins
Deposition Power #1:	50W	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:				Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:			/	Comments					
Total Sputter Time (all sample holders combined) Target #1			5mins	Total Sputter Time (all sample holders) Target #2					

Name/Date:	ROHIT SHARMA	Date:	08/27/10	Start Time	4:30	End Time	5:48	Load lock BP	—
Process Gas (es)	Ar/150	Substrate:	Si	Deposition Pressure (mT)		—		Chamber BP	5x10-7
Target Material #1	Ti	Time:	10mins			Presput Power Film #1:		Time:	2 mins
Deposition Power #1:	90W	~~Time~~: Pressure	10mT	Film Thickness (nm):		Deposition rate (Å/s)			—
Target Material #2	Pt/Au	Time:	10/6mins			Presput Power Film #2:		Time:	2/2mins
Deposition Power #2:	90/90W	~~Time~~: Pressure	11/20mT	Film Thickness (nm):	—	Deposition rate (Å/s)			—
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Name/Date:	Shamita	Date:		Start Time	10:30	End Time	11:30	Load lock BP	
Process Gas (es)	Ar -	Substrate:	Cu	Deposition Pressure (mT)	10			Chamber BP	
Target Material #1	Pt	Time:	1min			Presput Power Film #1:		Time:	1min
Deposition Power #1:	50W	Time:		Film Thickness (nm):	8	Deposition rate (Å/s)			
Target Material #2	~~Au~~ —	Time:				Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:	1			Comments					
Total Sputter Time (all sample holders combined) Target #1			1min	Total Sputter Time (all sample holders) Target #2					

Comments:

TM Vacuum Sputter Deposition LOG

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Karum / Venu	Date:		Start Time	9:00	End Time	10:30
Process Gas (es)	Ar	Substrate:	Si_3N_4 / Si	Deposition Pressure (mT)		End Time	
Target Material #1	Cr	Time:	20 m	Presput Power Film #1:		Time:	
Deposition Power #1:	180W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	Cr	Time:	10 min	Presput Power Film #2:		Time:	
Deposition Power #2:	180W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments		Load lock BP	$2.6e^{-6}$	Chamber BP	5.7×10^{-7}
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Handwritten values in entry 3 whose reading is uncertain: the Process Gas reads "Ar/150" and the Chamber BP reads "2.7×10^-7".

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Jungwoo Park	Date:	8-24-10	Start Time	11:30pm	End Time	00:30AM
Process Gas (es)	Ar	Substrate:	SiO_2	Deposition Pressure (mT)	10mT		
Target Material #1	Cr	Time:	2min	Presput Power Film #1:		Time:	1min
Deposition Power #1:	50W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	Au	Time:	7min	Presput Power Film #2:		Time:	1min
Deposition Power #2:	50W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:	1	Comments		Load lock BP	8.8×10^{-7}	Chamber BP	3.0×10^{-7}
Total Sputter Time (all sample holders combined) Target #1	3min	Total Sputter Time (all sample holders) Target #2	8min				

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	ROHIT SHARMA	Date:	08/25/10	Start Time	5:30	End Time	7:00
Process Gas (es)	Ar/150	Substrate:	Si	Deposition Pressure (mT)			
Target Material #1	Ti/Pt	Time:	10/10mins	Presput Power Film #1:		Time:	2/2mins
Deposition Power #1:	90/90	~~Time:~~ Pressure	10/1mT	Film Thickness (nm):	—	Deposition rate (Å/s)	—
Target Material #2	Au	Time:	3 mins	Presput Power Film #2:		Time:	2mins
Deposition Power #2:	90W	~~Time:~~ Pressure	20mT	Film Thickness (nm):	—	Deposition rate (Å/s)	—
Number of Sample Holders With Substrates:		Comments		Load lock BP	—	Chamber BP	2.7×10^{-7}
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Venu	Date:		Start Time		End Time	
Process Gas (es)	Ar	Substrate:		Deposition Pressure (mT)			
Target Material #1	Cr	Time:	20min	Presput Power Film #1:		Time:	
Deposition Power #1:	180 W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	Cr	Time:	20min	Presput Power Film #2:		Time:	
Deposition Power #2:	180KW	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments		Load lock BP	$2.4e^{-6}$	Chamber BP	$6\times e^{-7}$
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date: Jung Woo Park		Date:	23 Aug 10	Start Time	10:00AM	End Time	11:[illegible]	Load lock BP	8.4×10-7
Process Gas (es)	Ar	Substrate: SiO2		Deposition Pressure (mT)	10	End Time		Chamber BP	2.6×10-7
Target Material #1	TiW	Time: 5min				Presput Power Film #1:		Time:	1 min
Deposition Power #1:	45W	Time:		Film Thickness (nm):	30nm	Deposition rate (Å/s)		6nm/min	
Target Material #2	Au	Time:				Presput Power Film #2:		Time:	1 min
Deposition Power #2:	200W	Time: 8min		Film Thickness (nm):	600nm	Deposition rate (Å/s)		75nm/min	
Number of Sample Holders With Substrates: 1				Comments					
Total Sputter Time (all sample holders combined) Target #1		6 min		Total Sputter Time (all sample holders) Target #2				9 min	

Name/Date: Jung Woo Park		Date:	23 Aug 10	Start Time	15:30	End Time		Load lock BP	8.4×10-7
Process Gas (es)	Ar	Substrate: SiO2		Deposition Pressure (mT)		10 mT		Chamber BP	2.6×10-7
Target Material #1	TiW	Time: 5 min				Presput Power Film #1: 45		Time:	1 min
Deposition Power #1:	45 W	Time:		Film Thickness (nm):	30 nm	Deposition rate (Å/s)		6nm/min	
Target Material #2	Au	Time:				Presput Power Film #2: 200		Time:	1 min
Deposition Power #2:	200W	Time: 8 min		Film Thickness (nm):	600 nm	Deposition rate (Å/s)		75 nm/min	
Number of Sample Holders With Substrates: 1				Comments					
Total Sputter Time (all sample holders combined) Target #1		6 min		Total Sputter Time (all sample holders) Target #2				9 min	

Name/Date: Jung Woo Park		Date:	23 Aug 10	Start Time	17:00	End Time	18:00	Load lock BP	7.0×10-7
Process Gas (es)	Ar	Substrate: Si		Deposition Pressure (mT)	10			Chamber BP	3.0×10-7
Target Material #1	Cr	Time: 3min				Presput Power Film #1:		Time:	1 min
Deposition Power #1:	500	Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2	Au	Time:				Presput Power Film #2:		Time:	1 min
Deposition Power #2:	50W	Time: 7 min		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates: 1				Comments					
Total Sputter Time (all sample holders combined) Target #1		4 min		Total Sputter Time (all sample holders) Target #2				8 min	

Name/Date: Jung Woo Park		Date:	8-24-10	Start Time	14:00	End Time	14:00	Load lock BP	
Process Gas (es)		Substrate:		Deposition Pressure (mT)				Chamber BP	
Target Material #1		Time:				Presput Power Film #1:		Time:	
Deposition Power #1:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Target Material #2		Time:				Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments					
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2					

Comments: I could not use TMV due to my samples were not ready. please e-mail me if you have any questions (cukmist@gmail.com).

TM Vacuum Sputter Deposition LOG

Name/Date: Mohit (Menon Group)			Date:	08/17	Start Time	1330	End Time	1515	Load lock BP	7.0x10-7
Process Gas (es)	Ar	Substrate:	Si	Deposition Pressure (mT)		10 mT	End Time		Chamber BP	2.0x10-7
Target Material #1	Pt	Time: 3 min				Presput Power Film #1:			Time:	2.0 min
Deposition Power #1:	90 W	Time:		Film Thickness (nm):			Deposition rate (Å/s)			
Target Material #2	—	Time:				Presput Power Film #2:			Time:	
Deposition Power #2:	—	Time:		Film Thickness (nm):			Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments						
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2						

Name/Date: TRIDIB GHOSH			Date:	08/17/10	Start Time	3:15	End Time	4:50	Load lock BP	1x10-6
Process Gas (es)	Ar	Substrate: Glass		Deposition Pressure (mT)		10 mTorr			Chamber BP	4.4x10-7
Target Material #1	Ti/W	Time:				Presput Power Film #1: 50W			Time:	2 min
Deposition Power #1:	50 W	Time:	16s	Film Thickness (nm):		2-3nm	Deposition rate (Å/s)			6-8 nm/min
Target Material #2	Au	Time:				Presput Power Film #2: 50W			Time:	2 min
Deposition Power #2:	50 W	Time:	2 min	Film Thickness (nm):		40 nm	Deposition rate (Å/s)			20 nm/min
Number of Sample Holders With Substrates: 2				Comments						
Total Sputter Time (all sample holders combined) Target #1			32 s	Total Sputter Time (all sample holders) Target #2					4 mins	

Name/Date: Raj (Blackrock Microsystems)			Date:	08/17	Start Time	5.00	End Time	5.30	Load lock BP	6.6x10-7
Process Gas (es)	Ar	Substrate:		Deposition Pressure (mT)		10 mT			Chamber BP	2.8x10-7
Target Material #1	Cr	Time: 10 Min.				Presput Power Film #1: 180W			Time:	2 Min.
Deposition Power #1:	180 W	Time:		Film Thickness (nm):			Deposition rate (Å/s)			
Target Material #2	—	Time:				Presput Power Film #2:			Time:	
Deposition Power #2:	—	Time:		Film Thickness (nm):			Deposition rate (Å/s)			
Number of Sample Holders With Substrates: 2				Comments						
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2						

Name/Date: Raj (Blackrock Micro)			Date:	08/20	Start Time		End Time		Load lock BP	6.2x10-7
Process Gas (es)	Ar	Substrate:		Deposition Pressure (mT)		10 mT			Chamber BP	3.2x10-7
Target Material #1	Cr	Time: 10 Min				Presput Power Film #1: 180			Time:	2 Min.
Deposition Power #1:	180	Time:		Film Thickness (nm):			Deposition rate (Å/s)			
Target Material #2		Time:				Presput Power Film #2:			Time:	
Deposition Power #2:		Time:		Film Thickness (nm):			Deposition rate (Å/s)			
Number of Sample Holders With Substrates:				Comments						
Total Sputter Time (all sample holders combined) Target #1				Total Sputter Time (all sample holders) Target #2						

Comments:

TM Vacuum Sputter Deposition LOG

Name/Date: Rohit Sharma | Date: 08/05/10 | Start Time: 3:15 | End Time: 6:30 | Load lock BP: —
Process Gas (es): Ar/150 | Substrate: Si | Deposition Pressure (mT): 150 | End Time: — | Chamber BP: 3.2 x 10^-7
Target Material #1: Ti | Time: 10 min / 10mT | Presput Power Film #1: | Time: 2 min
Deposition Power #1: 90W | Time: 10 min | Film Thickness (nm): — | Deposition rate (Å/s): —
Target Material #2: Pt/Au | Time: 11 min / 6 min | Presput Power Film #2: | Time: 2/2 min
Deposition Power #2: 90/90W | Time: Ar: 11/20mT | Film Thickness (nm): — | Deposition rate (Å/s): —
Number of Sample Holders With Substrates: | Comments:
Total Sputter Time (all sample holders combined) Target #1: | Total Sputter Time (all sample holders) Target #2:

Name/Date: Jannelu Steinbach ~~08/10/10~~ | Date: 08/10/10 | Start Time: 1:40 PM | End Time: 3 PM | Load lock BP: —
Process Gas (es): Ar | Substrate: Si | Deposition Pressure (mT): ~~150~~ | Chamber BP: 3.1 x 10^-1
Target Material #1: Ti | Time: 10 min / 10 mT | Presput Power Film #1: 50W | Time: 2 min
Deposition Power #1: 90 W | Time: | Film Thickness (nm): | Deposition rate (Å/s):
Target Material #2: | Time: | Presput Power Film #2: | Time:
Deposition Power #2: | Time: | Film Thickness (nm): | Deposition rate (Å/s):
Number of Sample Holders With Substrates: | Comments:
Total Sputter Time (all sample holders combined) Target #1: | Total Sputter Time (all sample holders) Target #2:

Name/Date: Layne Williams | Date: 8/11/10 | Start Time: 1:15 | End Time: 5:30 | Load lock BP: —
Process Gas (es): | Substrate: Glass, Si | Deposition Pressure (mT): 10 mT | Chamber BP: 2.7x^-7
Target Material #1: Ti | ~~Time:~~ Gas: Ar / 150 sccm | Presput Power Film #1: 90 | Time: 2 min
Deposition Power #1: 90 | Time: 10 min | Film Thickness (nm): | Deposition rate (Å/s):
Target Material #2: IrOx | ~~Time:~~ Gas: Ar/100 sccm, O2/100 sccm | Presput Power Film #2: 100 | Time: 12
Deposition Power #2: 100 | Time: 70 min | Film Thickness (nm): | Deposition rate (Å/s):
Number of Sample Holders With Substrates: 2 | Comments: 10 min post sputter on Ir
Total Sputter Time (all sample holders combined) Target #1: 20+2 | Total Sputter Time (all sample holders) Target #2: 140 min + 22 presput sputter

Name/Date: Bennion Redd | Date: 8/12/10 | Start Time: 10:10 | End Time: | Load lock BP: —
Process Gas (es): | Substrate: Pt, PR+COR | Deposition Pressure (mT): 10 | Chamber BP: 2.7x^-7
Target Material #1: IrOx | Time: 50 min. | Presput Power Film #1: | Time:
Deposition Power #1: | Time: | Film Thickness (nm): | Deposition rate (Å/s):
Target Material #2: | Time: | Presput Power Film #2: | Time:
Deposition Power #2: | Time: | Film Thickness (nm): | Deposition rate (Å/s):
Number of Sample Holders With Substrates: | Comments:
Total Sputter Time (all sample holders combined) Target #1: | Total Sputter Time (all sample holders) Target #2:

Comments: Chuck did not rotate. Proceeded anyway

TM Vacuum Sputter Deposition LOG

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Jung Woo Park / 8-1-10	Date:	8-1-10	Start Time	2:40 PM	End Time	3:50 PM
Load lock BP		Chamber BP					
Process Gas (es)	Ar	Substrate:		Deposition Pressure (mT)	10	End Time	
Target Material #1	Cr	Time:	2	Presput Power Film #1:		Time:	1
Deposition Power #1:	50W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	Au	Time:	3.5	Presput Power Film #2:		Time:	1
Deposition Power #2:	50W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:	2	Comments					
Total Sputter Time (all sample holders combined) Target #1	3	Total Sputter Time (all sample holders) Target #2	4.5				

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Yan Xue (?)	Date:	8/1/10	Start Time	4:30 PM	End Time	5:30 PM
Load lock BP		Chamber BP					
Process Gas (es)	Ar	Substrate:		Deposition Pressure (mT)	10		
Target Material #1	Au	Time:	2 min	Presput Power Film #1:		Time:	
Deposition Power #1:	50	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2		Time:		Presput Power Film #2:		Time:	
Deposition Power #2:		Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:	1	Comments					
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Luciano Aguirre (?)	Date:	8/3/10	Start Time	9:00	End Time	
Load lock BP		Chamber BP	5.3x10				
Process Gas (es)	Ar	Substrate:	Glass	Deposition Pressure (mT)	20		
Target Material #1	Ti	Time:	1 min	Presput Power Film #1:		Time:	
Deposition Power #1:	200W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	Ag	Time:	2.5 min	Presput Power Film #2:		Time:	
Deposition Power #2:	50W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:		Comments					
Total Sputter Time (all sample holders combined) Target #1		Total Sputter Time (all sample holders) Target #2					

Field	Value	Field	Value	Field	Value	Field	Value
Name/Date:	Sandeep (BR)	Date:	8/3/10	Start Time	3pm	End Time	5pm
Load lock BP	[illegible]	Chamber BP					
Process Gas (es)	Ar	Substrate:	Si	Deposition Pressure (mT)			
Target Material #1	Ti	Time:	5min	Presput Power Film #1:		Time:	
Deposition Power #1:	90W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Target Material #2	Ir	Time:	20min	Presput Power Film #2:		Time:	
Deposition Power #2:	100W	Time:		Film Thickness (nm):		Deposition rate (Å/s)	
Number of Sample Holders With Substrates:	ONE	Comments					
Total Sputter Time (all sample holders combined) Target #1	5min	Total Sputter Time (all sample holders) Target #2	20min				

Comments: Ir shutter was not opening. Staff fixed it